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ศูนย์วิทยทรัพยากร
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ภาคผนวก ก.
 โปรแกรมการวิเคราะห์ผลของสิ่งประดิษฐ์มอส
 เขียนโดย นาย ธนวิทย์ ชูลิกาวิทย์
 1 มกราคม 2531

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10      !!!!!!!!!!!!!!!!!!!!!!!
20      !! MAIN MENU PROGRAM !!
30      !!   "MENU"   !!
40      !!!!!!!!!!!!!!!!!!!!!!!
50      PRINT CHR$(112)
60      PRINT CHR$(132)
70      PRINT TABXY(15,2);"MOS's characteristics program on HENLETT PACKARD sy
stem."
80      PRINT CHR$(128)
90      PRINT TABXY(15,4);"                                BY Mr. Dhanavich chuli
kavit"
100     PRINT TABXY(15,6);"These programs are used for measuring the character
istics -"
110     PRINT TABXY(10,7);"of devices which are fabricated by MOS technology.O
n these pro -"
120     PRINT TABXY(10,8);"gram, sometime, the alpha and graphics are shown on t
he screen in-"
130     PRINT TABXY(10,9);"the same time.If you'd like to see clearly each one
,please press"
140     PRINT TABXY(10,10);"the ALPHA or GRAPHICS button to select the screen
which you'd -"
150     PRINT TABXY(10,11);"like to see."
160     PRINT CHR$(129)
170     PRINT TABXY(15,18);" WHEN YOU ARE READY,PLEASE PRESS THE 'CONTINUE' KE
Y. "
180     PAUSE
190     PRINT CHR$(112)
200     PRINT CHR$(128)
210     PRINT TABXY(10,6);"Please choose the program which you'd like to use,b
y press the -"
220     PRINT TABXY(10,7);"number of the option.
.
230     PRINT CHR$(132)
240     PRINT TABXY(21,9);"Option. ";TABXY(51,9);"Program."
250     PRINT CHR$(128)
260     PRINT TABXY(10,11);"                1                C-V Measureme
nt.
270     PRINT TABXY(10,12);"                2                Recall C-V Ch
aracteristics data."
280     PRINT TABXY(10,13);"                3                RESISTANCE Me
asurement.

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290     PRINT TABXY(10,14);"          4           Recall RESIST
ANCE data.
300     PRINT TABXY(10,15);"          5           MOSFET's thre
shold voltage.
310     PRINT TABXY(10,16);"          6           EXIT

320     BEEP
330     INPUT Op
340     IF Op<1 OR Op>6 THEN 330
350     ON Op GOTO 360,390,420,450,480,510
360     PRINT CHR$(129)
370     PRINT TABXY(22,11);" 1 "
380     LOAD "DHA"
390     PRINT CHR$(129)
400     PRINT TABXY(22,12);" 2 "
410     LOAD "DHA10"
420     PRINT CHR$(129)
430     PRINT TABXY(22,13);" 3 "
440     LOAD "RESIST"
450     PRINT CHR$(129)
460     PRINT TABXY(22,14);" 4 "
470     LOAD "RESIST_OUT"
480     PRINT CHR$(129)
490     PRINT TABXY(22,15);" 5 "
500     LOAD "MOS_T1"
510     PRINT CHR$(129)
520     PRINT TABXY(22,16);" 6 "
530     END

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10          !!!!!!!!!!!!!!!!!!!!!!!
11          !! MAIN PROGRAM !!
12          !!   "DHA"   !!
13          !!!!!!!!!!!!!!!!!!!!!!!
14
15 ! V(*) is the array keeping the values of voltage data.
16 ! C(*) is the array keeping the values of capacitance data.
17 ! G(*) is the array keeping the values of conductance data.
18 ! D(*) is the array keeping the values of disipation factor data.
19 ! Op  is the variable keeping the code number for choosing the mode of -
20 !      operation.
21
22          !-----!
23 COM V(700),C(700),G(700),D(700)
24 COM REAL K1,K2,Y,C$(5),K$(5)
25 COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
26          !-----!
27
28 PRINT CHR$(12)
29 PRINT CHR$(129)
30 PRINT TABXY(10,9);"PLEASE SELECT THE OPTION BY PRESS THE DESIRE NUMBER &
31 ENTER KEY."
32
33 PRINT TABXY(30,11);"1. MOS MEASUREMENT."
34 PRINT TABXY(30,13);"2. MOS ANALYSIS.  "
35
36 INPUT Op
37 IF Op<>1 AND Op<>2 THEN 210
38 IF Op=1 THEN
39     LOADSUB Set_cond FROM "DHA1"
40     Set_cond
41 ELSE
42     LOADSUB Analyse_data FROM "DHA8"
43     Analyse_data
44     GOTO 570
45
46 END IF
47 IF C$="X" THEN 570
48 LOADSUB Measure FROM "DHA5"
49 Measure
50 PRINT CHR$(12)
51 PRINT CHR$(131)
52 PRINT TABXY(10,10);" Would you like to save the data on disk ? (yes or no
53 ) "
54
55 INPUT P$
56 IF P$<>"Y" AND P$<>"y" AND P$<>"N" AND P$<>"n" THEN 370
57 IF P$="Y" OR P$="y" THEN
58     LOADSUB Record FROM "DHA14"
59     Record
60 ELSE
61     GOTO 440
62
63 END IF
64 PRINT CHR$(12)
65 PRINT CHR$(131)
66 PRINT TABXY(1,10);"Would you like to analyse the impotant parameter of MO
67 S cap.? ((Y)es or (N)o)."  

68
69 INPUT P$
70 IF P$<>"Y" AND P$<>"y" AND P$<>"N" AND P$<>"n" THEN 480
71 IF P$="Y" OR P$="y" THEN
72     LOADSUB Analyse_data FROM "DHA8"
73     Analyse_data
74 ELSE
75     GOTO 550
76
77 END IF
78 LOAD "MENU"
79 END

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10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20          !! MOS MEASUREMENT PROGRAM !!
30          !!      "DHA1"      !!
40          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
50  SUB Set_cond
60  ! K1,K2 are the set value of starting and final voltage, -
70  !   respectively, which the user want to choose, in range -32
80  !   to 32 volts.
90  ! Y   is the constant value for stepping up or down the gate-
100 !   voltage.
110 ! C$  keeps the frequency code to control the multi-frequency
120 !   LCR meter.
130 ! K$  keeps the code to choose the measured parameter from LCR meter.
140          !-----!
150  COM V(*),C(*),B(*),D(*)
160  COM REAL K1,K2,Y,C$,K$
170  COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
180          !-----!
190  PRINT CHR$(12)
200  PRINT CHR$(131)
210  PRINT TABXY(10,10); " Please connect your sample following this connect
ion. "
220  PRINT TABXY(10,11); " Metal oxide contact is connected to high terminal
of 4274A. "
230  PRINT TABXY(10,12); " Substrate contact is connected to low terminal of
4274A. "
240  PRINT CHR$(129)
250  PRINT TABXY(20,14); " Press continue key when you are ready. "
260  PAUSE
270          !-----!
280  PRINT CHR$(12)
290  PRINT CHR$(128)
300  PRINT TABXY(15,5); "ENTER VALUE STARTING VOLTAGE IN RANGE -32 TO 32."
310  INPUT K1
320  IF K1<-32 OR K1>32 THEN
330      PRINT TABXY(15,7); "DON'T BE SILLY, PLEASE GIVE THE VOLTAGE IN RANGE
-32 TO 32."
340      WAIT 3
350      PRINT TABXY(15,7); "
.
360      GOTO 310
370  END IF
380  PRINT CHR$(129)
390  PRINT TABXY(20,10); " STARTING VOLTAGE = ",K1," V. "
400  IF K1>0 THEN
410      Y=.2
420  ELSE
430      Y=-.2
440  END IF
450  PRINT CHR$(128)
460  PRINT TABXY(15,5); "ENTER THE VALUE OF FINAL VOLTAGE IN RANGE -32 TO 32
.
.
470  INPUT K2
480  IF K2<-32 OR K2>32 THEN
490      PRINT TABXY(15,7); "DON'T BE SILLY, PLEASE GIVE THE VOLTAGE IN RANGE
-32 TO 32."

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500     WAIT 3
510     PRINT TABXY(15,7);"
.
520     GOTO 470
530     END IF
540     PRINT CHR$(129)
550     PRINT TABXY(20,11);" FINAL VOLTAGE   = ",K2," V. "
560     PRINT CHR$(128)
570     PRINT TABXY(15,5);"
.
580                                     !-----!
590     WAIT 3
600     PRINT CHR$(12)
610     PRINT CHR$(128)
620     PRINT TABXY(7,10);"PLEASE CHOOSE THE FOLLOWING FREQUENCY CODE WHICH YO
U WANT TO OPERATE."
630     PRINT CHR$(129)
640     PRINT TABXY(15,12);" F11 FOR 100 Hz.      F17 FOR 4 KHz.      "
650     PRINT TABXY(15,13);" F12 FOR 120 Hz.      F18 FOR 10 KHz.     "
660     PRINT TABXY(15,14);" F13 FOR 200 Hz.      F19 FOR 20 KHz.     "
670     PRINT TABXY(15,15);" F14 FOR 400 Hz.      F20 FOR 40 KHz.     "
680     PRINT TABXY(15,16);" F15 FOR 1   KHz.      F21 FOR 100 KHz.    "
690     PRINT TABXY(15,17);" F16 FOR 2   KHz.      X TO EXIT THE PROGRAM."
700     INPUT C$
710     IF C$="X" THEN
720         BEEP
730         GOTO 880
740     ELSE
750         OUTPUT 717;C$
760     END IF
770                                     !-----!
780     PRINT CHR$(12)
790     PRINT CHR$(129)
800     PRINT TABXY(10,10);" If you want to measure C/B characteristic,press A
.
810     PRINT TABXY(10,11);" If you want to measure C/D characteristic,press a
ny key. "
820     INPUT K$
830     IF K$="A" THEN
840         OUTPUT 717;"A2B3"
850     ELSE
860         OUTPUT 717;"A2B1"
870     END IF
880     SUBEND

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10          !!!!!!!!!!!!!!!!!!!!!!!
20          !! INPUT DATA PROGRAM !!
30          !!   "DHA2"   !!
40          !!!!!!!!!!!!!!!!!!!!!!!
50 SUB Input
60 ! X      is each voltage value stepped up and down by Y.
70 ! I,J    are the counters of set of input data.
80 ! A,B,Amx,Amin,Bmx,Bmin,Vmx1,Vmx2,Vmin1,Vmin2 are the dummy
90 !       variables.
100 ! Vcmax,Vcmin are the values of voltage which capacitance is -
110 !           maximum and minimum, respectively.
120 ! Vgmax,Vgmin are the values of voltage which conductance is -
130 !           maximum and minimum, respectively.
140 ! Vdmax,Vdmin are the values of voltage which dispersion factor-
150 !           is maximum and minimum, respectively.
160 ! F$     keeps the name of data file which is created.
170 ! L      is the variable to point each set of data kept in files.
180 ! Msi    is the variable to keep the number of mass storage.
190          !-----!
200          COM V(*),C(*),B(*),D(*)
210          COM REAL K1,K2,Y,C$,K$
220          COM REAL Amx,Amin,Bmx,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
230          !-----!
240          PRINT CHR$(131)
250          PRINT TABXY(10,15); " Please wait a moment, program is running. "
260          FOR X=0 TO K1 STEP Y
270             OUTPUT 717;"B1";VAL$(X);"E";"00V";
280             WAIT .2
290          NEXT X
300          !-----!
310          I=0
320          FOR X=K1 TO K2 STEP -Y
330             I=I+1
340             OUTPUT 717;"B1";VAL$(X);"E";"00V";
350             WAIT .2
360             ENTER 717;A,B
370             IF X=K1 THEN
380                 Amx=A
390                 Bmx=B
400                 Vmx1=X
410                 Vmx2=X
420                 Amin=A
430                 Bmin=B
440                 Vmin1=X
450                 Vmin2=X
460             END IF
470             IF A>Amx THEN
480                 Amx=A
490                 Vmx1=X
500             END IF
510             IF A<Amin THEN
520                 Amin=A
530                 Vmin1=X
540             END IF
550             IF B>Bmx THEN

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560      Bmax=B
570      Vmax2=X
580      END IF
590      IF B<Bmin THEN
600          Bmin=B
610          Vmin2=X
620      END IF
630      V(I)=X
640      C(I)=A
650      Vcmax=Vmax1
660      Vcmin=Vmin1
670      IF K$="A" THEN
680          G(I)=B
690          Vgmax=Vmax2
700          Vgmin=Vmin2
710      ELSE
720          D(I)=B
730          Vdmax=Vmax2
740          Vdmin=Vmin2
750      END IF
760  NEXT X
770  J=1
780  FOR X=K2 TO K1 STEP Y
790      J=J+1
800      OUTPUT 717;"B1";VAL$(X);"E";"00V";
810      WAIT .2
820      ENTER 717;A,B
830      V(J)=X
840      C(J)=A
850      IF K$="A" THEN
860          G(J)=B
870      ELSE
880          D(J)=B
890      END IF
900  NEXT X
910  REDIM V(J),C(J),G(J),D(J)
920  !-----!
930  FOR X=K1 TO 0 STEP -Y
940      OUTPUT 717;"B1";VAL$(X);"E";"00V";
950      WAIT .2
960  NEXT X
970  SUBEND

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10      !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20      !! SCALING AND DRAW X-Y AXIS !!
30      !!   IN LINEAR SCALE   !!
40      !!   "DHA3"           !!
50      !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
60      SUB Scaling
70      ! Wl,Wr,Wb,Wt   are the variables setting the reference of scaling.
80      ! Cal,Car,Cab,Cat are the variables setting the boundary of axes.
90      ! Cfl,Cfr,Cfb,Cft are the variables setting the boundary of graphics.
100     ! Xmax_gdu,Ymax_gdu are the parameter of screen
110     ! Xtick,Ytick,Xloxy |
120     ! Yloxc,Xmajor,Size > are the parameters of the 'AXES' statement.
130     ! Ymajor         |
140     ! M               is the dummy variable.
150     !-----!
160     COM V(*),C(*),B(*),D(*)
170     COM REAL K1,K2,Y,C$,K$
180     COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
190     !-----!
200     Amaxx=Amax*10^12      ! Maximum value of the MOS CAP.
210     Aminx=Amin*10^12     ! Minimum value of the MOS CAP.
220     Xmax_gdu=100*RATIO   ! \ Set parameter of screen.
230     Ymax_gdu=100        ! /
240     Yloxc=20*INT(Aminx/20) ! Find pos. of X-axis on Y-axis.
250     Wl=MIN(K1,K2)-10    ! \
260     Wr=MAX(K1,K2)+10    ! \ Set relative boundary.
270     Wb=Yloxc-40        ! /
280     Wt=Amaxx*1.2       ! /
290     Cal=Wl+5           ! \
300     Car=Wr-5           ! \ Set parameter of soft clip.
310     Cab=Yloxc         ! /
320     Cat=Amaxx*1.1     ! /
330     Cfl=Cal-2         ! \
340     Cfr=Car+2         ! \ Set parameter of frame.
350     Cfb=Yloxc-30      ! /
360     Cft=Amaxx*1.15    ! /
370     Xtick=1           ! \
380     Ytick=10          ! \
390     Xloxy=0           ! \ Set parameter of axis.
400     Xmajor=5          ! /
410     Ymajor=5          ! /
420     Size=3           ! /
430     !-----!
440     GINIT
450     DEG
460     GRAPHICS ON
470     LORG 5             ! \
480     CSIZE 5           ! \
490     MOVE Xmax_gdu/2,.98*Ymax_gdu ! |
500     LABEL "C-V CHARACTERISTICS" ! |
510     CSIZE 4           ! |
520     MOVE Xmax_gdu/2,.93*Ymax_gdu ! |
530     IF C$="F11" THEN LABEL "Measure at 100 Hz" ! |
540     IF C$="F12" THEN LABEL "Measure at 120 Hz" ! \
550     IF C$="F13" THEN LABEL "Measure at 200 Hz" ! > Label head of graph.

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560 IF C$="F14" THEN LABEL "Measure at 400 Hz" ! /
570 IF C$="F15" THEN LABEL "Measure at 1 KHz" ! |
580 IF C$="F16" THEN LABEL "Measure at 2 KHz" ! |
590 IF C$="F17" THEN LABEL "Measure at 4 KHz" ! |
600 IF C$="F18" THEN LABEL "Measure at 10 KHz" ! |
610 IF C$="F19" THEN LABEL "Measure at 20 KHz" ! |
620 IF C$="F20" THEN LABEL "Measure at 40 KHz" ! /
630 IF C$="F21" THEN LABEL "Measure at 100 KHz"!/
640 VIEWPORT .02*Xmax_gdu,.98*Xmax_gdu,.02*Ymax_gdu,.9*Ymax_gdu!\
650 WINDOW W1,Wr,Wb,Wt ! |
660 CLIP Cal,Car,Cab,Cat ! \
670 AXES Xtick,Ytick,Xlocx,Ylocx,Xmajor,Ymajor,Size ! > Line.
680 CLIP OFF ! / scale
690 CLIP Cfl,Cfr,Cfb,Cft ! |
700 FRAME !/
710
720 LORG 7 !\
730 FOR M=Ylocx TO Cat STEP 50 !\
740 MOVE Xlocy,M !\
750 CSIZE 4,.4 !\
760 LABEL M ! \ Label Y-axis.
770 NEXT M !/
780 MOVE 0,Cat !/
790 IMOVE -3,0 !/
800 LDIR 90 !/
810 LABEL "CAPACITANCE (pF)" !/
820 LORG 6 !\
830 LDIR 360 !\
840 FOR M=Cal TO Car STEP 1 !\
850 MOVE M,Ylocx !\
860 IF M MOD 5=0 THEN LABEL M ! > Label X-axis.
870 NEXT M !/
880 LORG 5 !/
890 IMOVE -5,-10 !/
900 LABEL "VOLTAGE (V)" !/
910 SUBEND

```

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```

10                                     !!!!!!!!!!!!!!!!!!!!!
20                                     !! PLOT PROGRAM !!
30                                     !! IN LINEAR SCALE !!
40                                     !! "DHA4" !!
50                                     !!!!!!!!!!!!!!!!!!!!!
60 SUB Plot_linear
70 ! O is the pointer variable.
80 ! P$ is the variable to keep the answer string.
90                                     !-----!
100 COM V(#),C(#),B(#),D(#)
110 COM REAL K1,K2,Y,C$,K$
120 COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
130 DIM Cx(700)
140                                     !-----!
150 GRAPHICS ON
160 Cx(1)=C(1)*10^12 !\
170 MOVE V(1),Cx(1) !\
180 DRAW V(1),Cx(1) !\
190 FOR O=2 TO I ! > Plot curve with increasing volt.
200 Cx(O)=C(O)*10^12 ! /
210 DRAW V(O),Cx(O) ! /
220 NEXT O !/
230 FOR O=I+1 TO J !\
240 Cx(O)=C(O)*10^12 ! \ Plot curve with decreasing voltage.
250 DRAW V(O),Cx(O) ! /
260 NEXT O !/
270                                     !-----!
280 PRINT CHR$(12)
290 PRINT CHR$(129)
300 PRINT TABXY(10,10); " Would you like to have a paper of your C/V curve
? (y or n) "
310 INPUT P$
320 IF P$(<)"Y" AND P$(<)"y" AND P$(<)"N" AND P$(<)"n" THEN 310
330 IF P$="N" OR P$="n" THEN 470
340 PRINT TABXY(10,10); " If you would like to print the curve by printer,p
lease press key 'A'. "
350 PRINT TABXY(10,11); " If you would like to plot the curve by plotter,pl
ease press any key. "
360 INPUT Pr$
370 IF Pr$="A" THEN
380 PRINT CHR$(131)
390 PRINT TABXY(25,16); " PRINTER IS READY,PRESS CONTINUE KEY "
400 PAUSE
410 PRINT CHR$(12)
420 DUMP GRAPHICS #701
430 ELSE
440 LOADSUB Plotter FROM "DHA10"
450 Plotter
460 PRINT CHR$(12)
470 END IF
480 GRAPHICS OFF
490 SUBEND

```

```

10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20          !! C-V AND G-V MEASUREMENT !!
30          !!      "DHA5"      !!
40          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
50  SUB Measure
60          !-----!
70  COM V(*),C(*),B(*),D(*)
80  COM REAL K1,K2,Y,C#,K#
90  COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
100         !-----!
110  LOADSUB Input FROM "DHA2"      !\ Input data from LCR meter.
120  Input                          !/
130  IF K#="A" THEN
140      PRINT CHR$(12)
150      PRINT CHR$(129)
160      PRINT TABXY(10,10);" IF YOU WANT TO SEE C-V CURVE,PLEASE PRESS ";CH
R$(131);"C";CHR$(129);" KEY "
170      PRINT TABXY(10,11);"
.
180      PRINT TABXY(10,12);" IF YOU WANT TO SEE G-V CURVE;PLEASE PRESS ";CH
R$(131);"ANY";CHR$(129);" KEY "
190      ELSE
200      PRINT CHR$(12)
210      PRINT CHR$(129)
220      PRINT TABXY(10,10);" IF YOU WANT TO SEE C-V CURVE,PLEASE PRESS ";CH
R$(131);"C";CHR$(129);" KEY "
230      PRINT TABXY(10,11);"
.
240      PRINT TABXY(10,12);" IF YOU WANT TO SEE D-V CURVE;PLEASE PRESS ";CH
R$(131);"ANY";CHR$(129);" KEY "
250  END IF
260  INPUT T$
270  IF T#="C" THEN
280      LOADSUB Scaling FROM "DHA3"      !\
290      LOADSUB Plot_linear FROM "DHA4"  ! \ Plot data in linear scale.
300      Scaling                          !/
310      Plot_linear                       !/
320      PRINT CHR$(12)
330      PRINT CHR$(129)
340      PRINT TABXY(10,10);"Would you like to see another curve ? ((Y)es or
(N)o."
350      INPUT P$
360      IF P#<"Y" AND P#<"y" AND P#<"N" AND P#<"n" THEN 350
370      IF P#="Y" OR P#="y" THEN
380          PRINT CHR$(129)
390          PRINT TABXY(10,12);" Would you like to see G-V curve in ";CHR$(1
31);"(S);CHR$(129);"emilog or ";CHR$(131);"(L);CHR$(129);"linear scale ? "
400          INPUT W$
410          IF W#<"S" AND W#<"s" AND W#<"L" AND W#<"l" THEN 400
420          IF W#="S" OR W#="s" THEN
430              LOADSUB Semilog FROM "DHA6"      !\
440              LOADSUB Plot_semi FROM "DHA7"    ! \ Plot data in semilog
450              Semilog                          ! / scale.
460              Plot_semi                       !/
470              PRINT TABXY(10,14);" Would you like to see G-V curve in linea
r scale ? (Y)es or (N)o. "

```



```

480      INPUT P$
490      IF P$<>"Y" AND P$<>"y" AND P$<>"N" AND P$<>"n" THEN 480
500      IF P$="Y" OR P$="y" THEN
510          LOADSUB Scaling_con FROM "DHA11"      !\
520          LOADSUB Plot_linear_con FROM "DHA12"  ! \ Plot data in
530          Scaling_con                          ! / linear scale.
540          Plot_linear_con                      !/
550      ELSE
560          GOTO 570
570      END IF
580      ELSE
590          LOADSUB Scaling_con FROM "DHA11"      !\
600          LOADSUB Plot_linear_con FROM "DHA12"  ! \ Plot data in linear
610          Scaling_con                          ! / scale.
620          Plot_linear_con                      !/
630          PRINT TABXY(10,14); " Would you like to see G-V curve in semil
og scale ? (Y)es or (N)o. "
640      INPUT P$
650      IF P$<>"Y" AND P$<>"y" AND P$<>"N" AND P$<>"n" THEN 640
660      IF P$="Y" OR P$="y" THEN
670          LDADSUB Semilog FROM "DHA6"          !\
680          LOADSUB Plot_semi FROM "DHA7"        ! \ Plot data in semilog
690          Semilog                              ! / scale.
700          Plot_semi                            !/
710      ELSE
720          GOTO 730
730      END IF
740      END IF
750      ELSE
760          GOTO 770
770      END IF
780      ELSE
790          PRINT CHR$(12)
800          PRINT CHR$(129)
810          PRINT TABXY(10,12); " Would you like to see G-V curve in ";CHR$(131)
; "(S)";CHR$(129); "emilog or ";CHR$(131); "(L)";CHR$(129); "linear scale ? "
820      INPUT W$
830      IF W$<>"S" AND W$<>"s" AND W$<>"L" AND W$<>"l" THEN 820
840      IF W$="S" OR W$="s" THEN
850          LOADSUB Semilog FROM "DHA6"          !\
860          LOADSUB Plot_semi FROM "DHA7"        ! \ Plot data in semi-log
870          Semilog                              ! / scale.
880          Plot_semi                            !/
890          PRINT TABXY(10,14); " Would you like to see G-V curve in linear s
cale ? (Y)es or (N)o. "
900      INPUT P$
910      IF P$<>"Y" AND P$<>"y" AND P$<>"N" AND P$<>"n" THEN 900
920      IF P$="Y" OR P$="y" THEN
930          LOADSUB Scaling_con FROM "DHA11"
940          LOADSUB Plot_linear_con FROM "DHA12"
950          Scaling_con
960          Plot_linear_con
970      ELSE
980          GOTO 990
990      END IF

```

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```

1000     ELSE
1010     LOADSUB Scaling_con FROM "DHA11"    !\
1020     LOADSUB Plot_linear_con FROM "DHA12" ! \ Plot data in linear
1030     Scaling_con                       ! / scale.
1040     Plot_linear_con                   !/
1050     PRINT TABXY(10,14);" Would you like to see G-V curve in semilog
scale ? (Y)es or (N)o. "
1060     INPUT P$
1070     IF P$(">Y" AND P$(">y" AND P$(">N" AND P$(">n" THEN 1060
1080     IF P$="Y" OR P$="y" THEN
1090         LOADSUB Semilog FROM "DHA6"
1100         LOADSUB Plot_semi FROM "DHA7"
1110         Semilog
1120         Plot_semi
1130     ELSE
1140         GOTO 1150
1150     END IF
1160     END IF
1170     PRINT CHR$(12)
1180     PRINT TABXY(10,10);" Would you like to see another curve ? ((Y)es o
r (N)o. "
1190     INPUT P$
1200     IF P$(">Y" AND P$(">y" AND P$(">N" AND P$(">n" THEN 1190
1210     IF P$="Y" OR P$="y" THEN
1220         LOADSUB Scaling FROM "DHA3"    !\
1230         LOADSUB Plot_linear FROM "DHA4" ! \ Plot data in linear scale.
1240         Scaling                       ! /
1250         Plot_linear                   !/
1260     ELSE
1270         BOTO 1280
1280     END IF
1290     END IF
1300     SUBEND

```

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```

10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
11          !! SCALING AND DRAW AXIS !!
12          !! IN SEMI-LOG SCALE !!
13          !! "DHA6" !!
14          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
15
16 SUB Semilog
17 ! Bmaxl,Bminl are the variables to keep the logarithm value.
18 ! Bmaxli,Bainli are the variables to keep the integer value of the
19 ! logarithm value.
20 ! Xran
21 ! Yran
22 ! Xdiv
23 ! Ydiv
24 ! O,R
25 ! Wl,Wr,Wb,Wt are the variables setting the reference of scaling.
26 ! Xlocy,Ylocx are the parameters of the 'AXES' statement.
27
28 COM V(*),C(*),B(*),D(*)
29 COM REAL K1,K2,Y,C$,K$
30 COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
31
32 Bmaxx=ABS(Bmax*10^9) ! Maximum conductance value.
33 Bminx=ABS(Bmin*10^9) ! Minimum conductance value.
34 Bmaxl=LST(Bmaxx)
35 Bminl=LST(Bminx)
36 Bmaxli=INT(Bmaxl)
37 Bminli=INT(Bminl)
38 Xmax_gdu=100*RATIO ! Set parameter of screen.
39 Ymax_gdu=100
40 Wl=MIN(K1,K2)
41 Wr=MAX(K1,K2)
42 Wb=Bminli
43 IF FRACT(Bmaxl)=0 THEN
44   Wt=Bmaxli
45   Yran=Bmaxli-Bminli
46 ELSE
47   Wt=Bmaxli+1
48   Yran=Bmaxli-Bminli+1
49 END IF
50 Xran=MAX(K1,K2)-MIN(K1,K2)
51 Xdiv=.83*Xmax_gdu/Xran
52 Ydiv=.75*Ymax_gdu/Yran
53 Xlocy=Wb
54 Ylocx=Wl
55
56 GINIT
57 DEG
58 GRAPHICS ON
59 LORG 5
60 CSIZE 5
61 MOVE Xmax_gdu/2,.98*Ymax_gdu
62 LABEL "G-V CHARACTERISTICS"
63 CSIZE 4
64 MOVE Xmax_gdu/2,.93*Ymax_gdu
65 IF C$="F11" THEN LABEL "Measure at 100 Hz"
66 IF C$="F12" THEN LABEL "Measure st 120 Hz"

```

```

560 IF C$="F13" THEN LABEL "Measure at 200 Hz" ! > Label head of graph.
570 IF C$="F14" THEN LABEL "Measure at 400 Hz" ! /
580 IF C$="F15" THEN LABEL "Measure at 1 KHz" ! |
590 IF C$="F16" THEN LABEL "Measure at 2 KHz" ! |
600 IF C$="F17" THEN LABEL "Measure at 4 KHz" ! |
610 IF C$="F18" THEN LABEL "Measure at 10 KHz" ! |
620 IF C$="F19" THEN LABEL "Measure at 20 KHz" ! |
630 IF C$="F20" THEN LABEL "Measure at 40 KHz" ! /
640 IF C$="F21" THEN LABEL "Measure at 100 KHz" ! /
650 MOVE Xmax_gdu/2,.03*Ymax_gdu ! \
660 LABEL "GATE VOLTAGE (V)" ! \
670 CSIZE 3 ! \
680 FOR R=0 TO Xran ! > Label X-axis.
690 MOVE .15*Xmax_gdu+(R*Xdiv),.1*Ymax_gdu ! /
700 LABEL MIN(K1,K2)+R ! /
710 NEXT R ! /
720 LDIR 90 ! \
730 CSIZE 4 ! \
740 MOVE .01*Xmax_gdu,Ymax_gdu/2 ! |
750 LABEL "CONDUCTANCE (ns)" ! |
760 LDIR 0 ! |
770 CSIZE 3 ! |
780 FOR R=0 TO Yran ! |
790 MOVE 14,.15*Ymax_gdu+(R*Ydiv) ! |
800 IF Bminli+R=0 THEN ! |
810 LABEL "0" ! |
820 ELSE ! |
830 LABEL "10" ! > Label Y-axis.
840 END IF ! /
850 NEXT R ! /
860 FOR R=0 TO Yran ! |
870 MOVE 15,.15*Ymax_gdu+(R*Ydiv)+2 ! |
880 IF Bminli+R=0 THEN ! |
890 LABEL " " ! |
900 ELSE ! |
910 LABEL " ";Bminli+R ! |
920 END IF ! /
930 NEXT R ! /
940 VIEWPORT .15*Xmax_gdu,.98*Xmax_gdu,.15*Ymax_gdu,.9*Ymax_gdu ! \
950 WINDOW W1,Wr,Wb,Wt ! \
960 AXES 1,1,Xlocy,Ylocx ! |
970 GRID 1,1,0,0 ! |
980 PRINT CHR$(12) ! |
990 PRINT CHR$(128) ! |
1000 PRINT TABXY(0,10);"Would you like to draw the line between each order
of the scale ? ";CHR$(130);"Y";CHR$(128);"es OR ";CHR$(130);"N";CHR$(128);"o."
1010 INPUT P$
1020 IF P$(">Y" AND P$(">y" AND P$(">N" AND P$(">n" THEN 1010
1030 IF P$="N" OR P$="n" THEN 1110
1040 FOR D=Bminli TO Bmaxli ! \ Semi-
1050 FOR R=2 TO 9 ! > log
1060 Y=D+LGT(R) ! / scale
1070 MOVE MIN(K1,K2),Y ! |
1080 DRAW MAX(K1,K2),Y ! |
1090 NEXT R ! /
1100 NEXT D ! /
1110 SUBEND ! /

```

```

10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20          !!   PLOT PROGRAM   !!
30          !! IN SEMI-LOG SCALE !!
40          !!   "DHA7"   !!
50          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!
60  SUB Plot_semi
70  ! S   is the dummy variable.
80          !-----!
90          COM V(*),C(*),G(*),D(*)
100         COM REAL K1,K2,Y,C$,K$
110         COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
120         DIM Gx(700)
130         !-----!
140         GRAPHICS ON
150         Gx(1)=LGT(ABS(G(1)*10^9))
160         MOVE V(1),Gx(1)
170         DRAW V(1),Gx(1)
180         FOR S=2 TO I
190             Gx(S)=LGT(ABS(G(S)*10^9))
200             DRAW V(S),Gx(S)
210         NEXT S
220         FOR S=I+1 TO J
230             Gx(S)=LGT(ABS(G(S)*10^9))
240             DRAW V(S),Gx(S)
250         NEXT S
260         !-----!
270         PRINT CHR$(12)
280         PRINT CHR$(129)
290         PRINT TABXY(10,10); " Would you like to have a paper of your G/V curve
? (y or n) "
300         INPUT P$
310         IF P$(<>"Y" AND P$(<>"y" AND P$(<>"N" AND P$(<>"n" THEN 300
320         IF P$="N" OR P$="n" THEN 460
330         PRINT TABXY(10,10); " If you would like to print the curve by printer,p
lease press key 'A'. "
340         PRINT TABXY(10,11); " If you would like to plot the curve by plotter,pl
ease press any key. "
350         INPUT Pr$
360         IF Pr$="A" THEN
370             PRINT CHR$(131)
380             PRINT TABXY(25,16); " PRINTER IS READY,PRESS CONTINUE KEY "
390             PAUSE
400             PRINT CHR$(12)
410             DUMP GRAPHICS #701
420             ELSE
430             LOADSUB Plotter FROM "DHA9"
440             Plotter
450             PRINT CHR$(12)
460         END IF
470         GRAPHICS OFF
480         SUBEND

```

```

10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
11          !! MOS CAPACITANCE ANALYSIS !!
12          !!      "DHAB"      !!
13          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
14
15 SUB Analyse_data
16 ! St$      is the variable to keep the substrate's type.
17 ! Ga$      is the variable to keep the gate area's shape.
18 ! Di       is the variable to keep the gate area's diameter.
19 ! W        is the variable to keep the gate area's width.
20 ! L        is the variable to keep the gate area's length.
21 ! Ag       is the variable to keep the gate area.
22 ! Dox      is the variable to keep the gate oxide's thickness.
23 ! N        is the variable to keep the first assumption of substrate's -
24 !          concentration.
25 ! Csmn     is the variable to keep the minimum depletion region of cap.-
26 !          when the surface of substrate is inverted.
27 ! Ncon     is the variable to keep the substrate's concentration.
28 ! Cfbs     is the variable to keep the silicon surface capacitance at -
29 !          flatband in Farad.
30 ! Cfb      is the variable to keep the flatband capacitance in Farad.
31 ! Vfb1,Vfb2 is the variable to keep the flatband voltage in forward and -
32 !          backward ways,respectively.
33 ! Vfb      is the variable to keep the flatband voltage.
34 ! Mt       is the variable to keep the type number of the gate metal.
35 ! Wfm      is the variable to keep the vacuum work function of the gate
36 !          metal.
37 ! Wms      is the variable to keep the work function difference between
38 !          the gate metal and the semiconductor substrate.
39 ! Ci       is the variable to keep the oxide capacitance per unit area -
40 !          in Farad/cm2.
41 ! Dss      is the variable to keep the interfacial state density.
42          !-----!
43 COM V(*),C(*),G(*),D(*)
44 COM REAL K1,K2,Y,C$,K$
45 COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
46          !-----!
47 T=300      ! Room temperature in Kelvin.
48 Kb=1.38E-23 ! Boltzman constant.
49 Q=1.602E-19 ! Electron charge.
50 Ni=1.5E+10  ! Intrinsic concentration of Si at 300 K.
51 Eo=8.854E-14 ! Vacuum permittivity.
52 Eox=3.9      ! SiO2 relative permittivity.
53 Es=11.7     ! Si relative permittivity.
54 Eg=1.12     ! Band gap energy of Si.
55 Eafs=4.23   ! Electron affinity of Si.
56          !-----!
57          ! Find type of substrate and the gate oxide's thickness. !
58          !-----!
59 IF Op=2 THEN
60 PRINT CHR$(12)
61 PRINT CHR$(13)
62 PRINT TABXY(1,1);"Please input the maximum capacitance (in pF)."  

63 INPUT Amax
64 IF Amax<=0 THEN 530
65 PRINT TABXY(1,1);"Please input the minimum capacitance (in pF)."  


```

```

560     INPUT Amin
570     IF Amin<=0 THEN 560
580     PRINT TABXY(1,1);"Please input type of substrate ((N)-type or (P)-t
ype)."

```

```

1030      IF W<=0 THEN 1020
1040      PRINT TABXY(1,1);"Please input your rectangular gate's length (i
n cm.)
1050      INPUT L
1060      IF L<=0 THEN 1050
1070      Ag=W*L
1080      END IF
1090      GOTO 1130
1100      PRINT TABXY(1,1);"Please input your gate area (in cm2.)

1110      INPUT Ag
1120      IF Ag<=0 THEN 1110
1130      PRINT CHR$(128)
1140      PRINT TABXY(5,7);"Gate area is ";TAB(49);Ag;TAB(70);" cm2"
1150      Dox=Eo*Eox*Ag/Cox
1160      PRINT TABXY(5,8);"Oxide layer thickness is ";TAB(49);Dox#1.0E+8;TAB(70
);" angst."
1170      !-----!
1180      ! Find doping concentration of substrate. !
1190      !-----!
1200      PRINT CHR$(131)
1210      PRINT TABXY(1,1);"Is your substrate Si ? ((Y)es or (N)o).
"
1220      INPUT P$
1230      IF P$<>"Y" AND P$<>"y" AND P$<>"N" AND P$<>"n" THEN 1220
1240      IF P$="N" OR P$="n" THEN
1250      PRINT TABXY(1,1);"Please input relative permittivity of your substr
ate."
1260      INPUT Es
1270      IF Es<=0 THEN 1260
1280      PRINT TABXY(1,1);"Please input band gap energy of your substrate.

1290      INPUT Eg
1300      IF Eg<=0 THEN 1290
1310      PRINT TABXY(1,1);"Please input electron affinity of your substrate.

1320      INPUT Eafs
1330      IF Eafs<=0 THEN 1320
1340      END IF
1350      PRINT CHR$(128)
1360      PRINT TABXY(5,9);"Relative permittivity of substrate is ";TAB(49);Es
1370      N=1.0E+22
1380      Csm=(Cox*Cmin)/(Cox-Cmin)
1390      Ncon=4*Kb*T*LOG(N/Ni)*(Csm/Ag/Q)^2/Es/Eo
1400      IF (1-Ncon/N)<1.0E-4 THEN
1410      PRINT TABXY(5,10);"Doping concentration is ";TAB(49);Ncon;TAB(70);"
/cm3"
1420      ELSE
1430      N=Ncon
1440      GOTO 1390
1450      END IF
1460      !-----!
1470      ! Find flatband capacitance. !
1480      !-----!
1490      Cfs=(Es*Eo*Q^2*Ncon/Kb/T)^(.5)

```



```

1500 PRINT TABXY(5,11);"Silicon surface capacitance per unit -"
1510 PRINT TABXY(5,12);"area at flatband is ";TAB(49);Cfbs*1.0E+12;TAB(70);
" pF/cm2"
1520 Cfbs=Cfbs*Ag
1530 PRINT TABXY(5,13);"Silicon surface capacitance at flatband is ";TAB(49);
);Cfbs*1.0E+12;TAB(70);" pF"
1540 Cfb=Cfbs*Cox/(Cfbs+Cox)
1550 PRINT TABXY(5,14);"Flatband capacitance is ";TAB(49);Cfb*1.0E+12;TAB(7
0);" pF"
1560
1570
1580
1590 IF C(1)>C(1) THEN
1600 Dd=1
1610 E=1
1620 F=1
1630 ELSE
1640 Dd=1
1650 E=1
1660 F=-1
1670 END IF
1680 FOR Gg=Dd TO E STEP F
1690 IF C(Gg)<=Cfb THEN
1700 GOTO 1750
1710 ELSE
1720 GOTO 1740
1730 END IF
1740 NEXT Gg
1750 IF C(Gg)<>Cfb THEN
1760 H=C(Gg-1)-C(Gg)
1770 Ha=Cfb-C(Gg)
1780 Hb=Ha/H
1790 Va=ABS(V(Gg-1)-V(Gg))
1800 Vb=Va*Hb
1810 IF V(Gg-1)>V(Gg) THEN
1820 Vfb1=V(Gg)+Vb
1830 ELSE
1840 Vfb1=V(Gg)-Vb
1850 END IF
1860 ELSE
1870 Vfb1=V(Gg)
1880 END IF
1890 IF C(J)>C(1) THEN
1900 Dd=J
1910 E=1
1920 F=-1
1930 ELSE
1940 Dd=1
1950 E=J
1960 F=1
1970 END IF
1980 FOR Gg=Dd TO E STEP F
1990 IF C(Gg)<=Cfb THEN
2000 GOTO 2050
2010 ELSE

```

 ! Find the flatband voltage. !

Find flatband voltage on
 the first way.

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2020         GOTO 2040           ! \.
2030     END IF                 ! \ Find flatband voltage on
2040     NEXT Gg                 ! / the back way.
2050     IF C(Gg)<>Cfb THEN     ! /
2060         H=C(Gg+1)-C(Gg)   ! |
2070         Ha=Cfb-C(Gg)      ! |
2080         Hb=Ha/H            ! |
2090         Va=ABS(V(Gg+1)-V(Gg)) ! |
2100         Vb=Va#Hb          ! |
2110         IF V(Gg+1)>V(Gg) THEN ! |
2120             Vfb2=V(Gg)+Vb ! |
2130         ELSE                ! |
2140             Vfb2=V(Gg)-Vb ! |
2150         END IF             ! |
2160     ELSE                    ! |
2170         Vfb2=V(Gg)         ! /
2180     END IF                 !/
2190     Vfb=(Vfb1+Vfb2)/2
2200     PRINT TABXY(5,15);"Flatband voltage is ";TAB(49);Vfb;TAB(70);" V"
2210     !-----!
2220     ! Find work function difference and interfacial state density. !
2230     !-----!
2240     PRINT CHR$(131)
2250     PRINT TABXY(1,1);"Please select type of gate metal you used,Mg,Al,Ni,C
u,Ag,Au or the other metal"
2260     PRINT TABXY(1,2);" (1-7)."

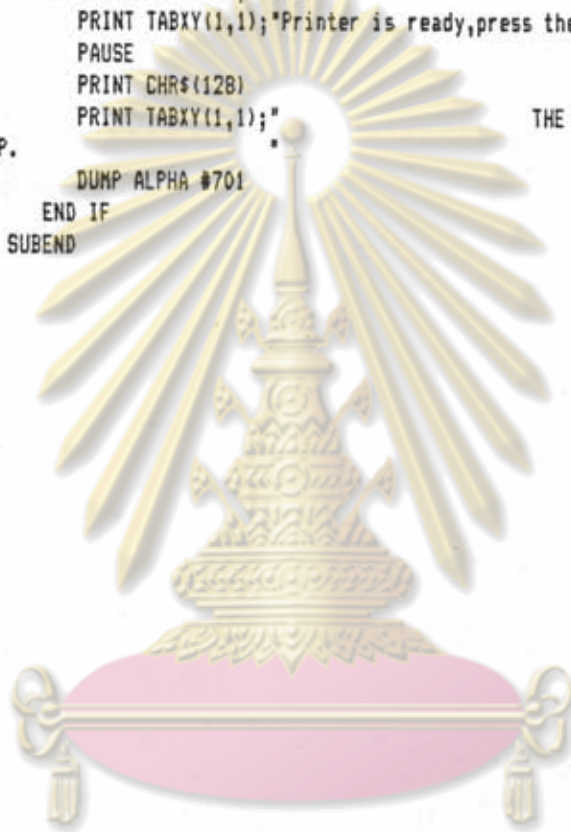
2270     INPUT Mt
2280     IF Mt<=0 OR Mt>=8 THEN 2270
2290     ON Mt GOTO 2300,2320,2340,2360,2380,2400,2420
2300     Wfm=3.7                ! Vacuum work function of Mg.
2310     GOTO 2440
2320     Wfm=4.2                ! Vacuum work function of Al.
2330     GOTO 2440
2340     Wfm=4.74               ! Vacuum work function of Ni.
2350     GOTO 2440
2360     Wfm=4.52               ! Vacuum work function of Cu.
2370     GOTO 2440
2380     Wfm=4.31               ! Vacuum work function of Ag.
2390     GOTO 2440
2400     Wfm=4.7                ! Vacuum work function of Au.
2410     GOTO 2440
2420     PRINT TABXY(1,1);"Please input work function of gate metal."
2430     INPUT Wfm
2440     IF Wfm<=0 THEN 2430
2450     PRINT CHR$(128)
2460     PRINT TABXY(5,16);"Vacuum work function of gate metal is ";TAB(49);Wfm
;TAB(70);" V"
2470     IF St$="N" OR St$="n" THEN
2480         Wms=Wfm-(Eafs-Eg/2-Kb*T*LOG(Ncon/Ni))
2490     ELSE
2500         Wms=Wfm-(Eafs-Eg/2-Kb*T*LOG(Ni/Ncon))
2510     END IF
2520     PRINT TABXY(5,17);"Work function difference is ";TAB(49);Wms;TAB(70);"
V"

```

```

2530 Ci=Cox/Ag
2540 Qss=(Wms-Vfb)*Ci/Q
2550 PRINT TABXY(5,18);"Interfacial state density is ";TAB(49);Qss;TAB(70);
    "/cm2"
2560 PRINT CHR$(131)
2570 PRINT TABXY(1,1);"Would you like to print the result to the printer ?
    ((Y)es or (N)o). "
2580 INPUT P$
2590 IF P$(">Y" AND P$(">y" AND P$(">N" AND P$(">n" THEN 2580
2600 IF P$="Y" OR P$="y" THEN
2610 PRINT TABXY(1,1);"Printer is ready,press the CONTINUE key."
2620 PAUSE
2630 PRINT CHR$(128)
2640 PRINT TABXY(1,1);" THE IMPORTANT PARAMETER OF
MOS CAP.
2650 DUMP ALPHA #701
2660 END IF
2670 SUBEND

```



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```

10      !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20      !!                               MAIN PROGRAM                               !!
30      !! C-V CHARACTERISTICS (RECALL THA DATA FROM THE DISC) !!
40      !!                               "DHA10"                               !!
50      !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
60      COM V(700),C(700),B(700),D(700)
70      COM REAL K1,K2,Y,C$(5),K$(5)
80      COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
90      !-----!
100     PRINT CHR$(12)
110     PRINT CHR$(129)
120     PRINT TABXY(10,10);" Please input the name of file which you want to reca
11 the data. "
130     INPUT F$
140     PRINT CHR$(12)
150     PRINT CHR$(129)
160     PRINT TABXY(10,10);" WOULD YOU LIKE TO RECALL YOUR DATA FROM MSI # ";CHR$(
(131);"0";CHR$(129);" OR # ";CHR$(131);" 1";CHR$(129);" ?"
170     INPUT Msi
180     IF Msi=0 OR Msi=1 THEN 240
190         PRINT CHR$(128)
200         PRINT TABXY(10,12);" PLEASE PRESS ONLY '0' OR '1'. "
210         WAIT 3
220         PRINT TABXY(10,12);"
230         GOTO 170
240     IF Msi=0 THEN
250         MASS STORAGE IS ":,700,0"
260     ELSE
270         MASS STORAGE IS ":,700,1"
280     END IF
290     ASSIGN @File TO F$
300     ENTER @File,1;Amax
310     ENTER @File,2;Bmax
320     ENTER @File,3;Amin
330     ENTER @File,4;Bmin
340     ENTER @File,5;Vmax1
350     ENTER @File,6;Vmax2
360     ENTER @File,7;Vmin1
370     ENTER @File,8;Vmin2
380     ENTER @File,9;C$
390     ENTER @File,10;I
400     ENTER @File,11;J
410     FOR L=1 TO J
420         ENTER @File,L+11;V(L),C(L),B(L)
430     NEXT L
440     MASS STORAGE IS ":,700,1"
450     K1=V(1)
460     K2=V(1)
470     Vcmax=Vmax1
480     Vcmin=Vmin1
490     Vgmax=Vmax2
500     Vgmin=Vmin2
510     Po=POS(F$,"CG")
520     IF Po<>0 THEN
530         PRINT CHR$(12)

```



```

1000     LOADSUB Scaling_con FROM "DHA11"
1010     LOADSUB Plot_linear_con FROM "DHA12"
1020     PRINT CHR$(12)
1030     Scaling_con
1040     Plot_linear_con
1050     PRINT TABXY(10,14);" Would you like to see G-V curve in semilog
scale ? (Y)es or (N)o. "
1060     INPUT P$
1070     IF P$(">Y" AND P$(">y" AND P$(">N" AND P$(">n" THEN 1060
1080     IF P$="Y" OR P$="y" THEN
1090         LOADSUB Semilog FROM "DHA6"
1100         LOADSUB Plot_semi FROM "DHA7"
1110         PRINT CHR$(12)
1120         Semilog
1130         Plot_semi
1140     ELSE
1150         GOTO 1160
1160     END IF
1170     END IF
1180     ELSE
1190         GOTO 1200
1200     END IF
1210     ELSE
1220     PRINT CHR$(12)
1230     PRINT CHR$(129)
1240     PRINT TABXY(10,12);" Would you like to see G-V curve in ";CHR$(131);"(
S)";CHR$(129);"emilog or ";CHR$(131);"(L)";CHR$(129);"linear scale ? "
1250     INPUT K$
1260     IF K$(">S" AND K$(">s" AND K$(">L" AND K$(">l" THEN 1250
1270     IF K$="S" OR K$="s" THEN
1280         LOADSUB Semilog FROM "DHA6"
1290         LOADSUB Plot_semi FROM "DHA7"
1300         PRINT CHR$(12)
1310         Semilog
1320         Plot_semi
1330         PRINT TABXY(10,14);" Would you like to see G-V curve in linear scal
e ? (Y)es or (N)o. "
1340     INPUT P$
1350     IF P$(">Y" AND P$(">y" AND P$(">N" AND P$(">n" THEN 1340
1360     IF P$="Y" OR P$="y" THEN
1370         LOADSUB Scaling_con FROM "DHA11"
1380         LOADSUB Plot_linear_con FROM "DHA12"
1390         PRINT CHR$(12)
1400         Scaling_con
1410         Plot_linear_con
1420     ELSE
1430         GOTO 1440
1440     END IF
1450     ELSE
1460         LOADSUB Scaling_con FROM "DHA11"
1470         LOADSUB Plot_linear_con FROM "DHA12"
1480         PRINT CHR$(12)
1490         Scaling_con
1500         Plot_linear_con
1510         PRINT TABXY(10,14);" Would you like to see G-V curve in semilog sca
le ? (Y)es or (N)o. "

```

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```

1520 INPUT P$
1530 IF P$("<Y") AND P$("<y") AND P$("<N") AND P$("<n") THEN 1520
1540 IF P$="Y" OR P$="y" THEN
1550     LOADSUB Semilog FROM "DHA6"
1560     LOADSUB Plot_semi FROM "DHA7"
1570     PRINT CHR$(12)
1580     Semilog
1590     Plot_semi
1600     ELSE
1610     GOTO 1620
1620 END IF
1630 END IF
1640 PRINT CHR$(12)
1650 PRINT CHR$(129)
1660 PRINT TABXY(10,10);"Would you like to see another curve ? ((Y)es or (N)
)o. "
1670 INPUT P$
1680 IF P$("<Y") AND P$("<y") AND P$("<N") AND P$("<n") THEN 1670
1690 IF P$="Y" OR P$="y" THEN
1700     LOADSUB Scaling FROM "DHA3"
1710     LOADSUB Plot_linear FROM "DHA4"
1720     PRINT CHR$(12)
1730     Scaling
1740     Plot_linear
1750     ELSE
1760     GOTO 1770
1770 END IF
1780 END IF
1790 PRINT CHR$(12)
1800 PRINT CHR$(131)
1810 PRINT TABXY(1,18);" Would you like to analyse the impotent parameter of M
DS cap? ((Y)es or (N)o). "
1820 INPUT P$
1830 IF P$("<Y") AND P$("<y") AND P$("<N") AND P$("<n") THEN 1820
1840 IF P$="Y" OR P$="y" THEN
1850     LOADSUB Analyse_data FROM "DHA8"
1860     Analyse_data
1870     ELSE
1880     GOTO 1890
1890 END IF
1900 LOAD "MENU"
1910 END

```

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```

10
20
30
40
50
60
70 SUB Scaling_con
80 ! Wl,Wr,Wb,Wt are the variables setting the reference of scaling.
90 ! Cal,Car,Cab,Cat are the variables setting the boundary of axes.
100 ! Cfl,Cfr,Cfb,Cft are the variables setting the boundary of graphics.
110 ! Xmax_gdu,Ymax_gdu are the parameter of screen
120 ! Xtick,Ytick,Xlocy !
130 ! Ylocx,Xmajor,Size > are the parameters of the 'AXES' statement.
140 ! Ymajor !
150 ! M is the dummy variable.
160
170 COM V(*),C(*),B(*),D(*)
180 COM REAL K1,K2,Y,C$,K$
190 COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Dp
200
210 Bmaxx=Bmax*10^7 ! Maximum value of the MOS CON.
220 Bminx=Bmin*10^7 ! Minimum value of the MOS CON.
230 Xmax_gdu=100*RATIO ! \ Set parameter of screen.
240 Ymax_gdu=100 ! /
250 Ylocx=20*INT(Bminx/20) ! Find pos. of X-axis on Y-axis.
260 Wl=MIN(K1,K2)-10 ! \
270 Wr=MAX(K1,K2)+10 ! \ Set relative boundary.
280 Wb=Ylocx-40 ! /
290 Wt=Bmaxx*1.2 ! /
300 Cal=Wl+5 ! \
310 Car=Wr-5 ! \ Set parameter of soft clip.
320 Cab=Ylocx ! /
330 Cat=Bmaxx*1.1 ! /
340 Cfl=Cal-2 ! \
350 Cfr=Car+2 ! \ Set parameter of frame.
360 Cfb=Ylocx-30 ! /
370 Cft=Bmaxx*1.15 ! /
380 Xtick=1 ! \
390 Ytick=10 ! \
400 Xlocy=0 ! \ Set parameter of axis.
410 Xmajor=5 ! /
420 Ymajor=5 ! /
430 Size=3 ! /
440
450 GINIT
460 DEG
470 GRAPHICS ON
480 LORG 5 ! \
490 CSIZE 5 ! \
500 MOVE Xmax_gdu/2,.98*Ymax_gdu ! |
510 LABEL "G-V CHARACTERISTICS" ! |
520 CSIZE 4 ! |
530 MOVE Xmax_gdu/2,.93*Ymax_gdu ! |
540 IF C$="F11" THEN LABEL "Measure at 100 Hz" ! |
550 IF C$="F12" THEN LABEL "Measure at 120 Hz" ! \

```



```

560 IF C$="F13" THEN LABEL "Measure at 200 Hz" ! > Label head of graph.
570 IF C$="F14" THEN LABEL "Measure at 400 Hz" ! /
580 IF C$="F15" THEN LABEL "Measure at 1 KHz" ! |
590 IF C$="F16" THEN LABEL "Measure at 2 KHz" ! |
600 IF C$="F17" THEN LABEL "Measure at 4 KHz" ! |
610 IF C$="F18" THEN LABEL "Measure at 10 KHz" ! |
620 IF C$="F19" THEN LABEL "Measure at 20 KHz" ! |
630 IF C$="F20" THEN LABEL "Measure at 40 KHz" ! /
640 IF C$="F21" THEN LABEL "Measure at 100 KHz" ! /
650 VIEWPORT .02*Xmax_gdu,.98*Xmax_gdu,.02*Ymax_gdu,.9*Ymax_gdu!\
660 WINDOW Wl,Wr,Wb,Wt ! |
670 CLIP Cal,Car,Cab,Cat ! | \
680 AXES Xtick,Ytick,Xlocy,Ylocx,Xmajor,Ymajor,Size ! > Line.
690 CLIP OFF ! / scale
700 CLIP Cfl,Cfr,Cfb,Cft ! |
710 FRAME ! /
720
730 LORG 7
740 FOR M=Ylocx TO Cat STEP 50
750     MOVE Xlocy,M
760     CSIZE 4,.4
770     LABEL M
780 NEXT M
790 MOVE 0,Cat
800 IMOVE -3,0
810 LDIR 90
820 LABEL "CONDUCTANCE*100 (nS)"
830 LORG 6
840 LDIR 360
850 FOR M=Cal TO Car STEP 1
860     MOVE M,Ylocx
870     IF M MOD 5=0 THEN LABEL M
880 NEXT M
890 LORG 5
900 IMOVE -5,-10
910 LABEL "VOLTAGE (V)"
920 SUBEND

```

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```

10                                     !!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20                                     !!   PLOT PROGRAM   !!
30                                     !!  IN LINEAR SCALE  !!
40                                     !!  FOR THE CONDUCTANCE !!
50                                     !!   "DHA12"   !!
60                                     !!!!!!!!!!!!!!!!!!!!!!!!!!!!!
70  SUB Plot_linear_con
80  ! 0   is the pointer variable.
90  ! P$  is the variable to keep the answer string.
100                                     !-----!
110  COM V(*),C(*),G(*),D(*)
120  COM REAL K1,K2,Y,C$,K$
130  COM REAL Amax,Amin,Bmax,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
140  DIM Gx(700)
150                                     !-----!
160  GRAPHICS ON
170  Gx(1)=G(1)*10^7
180  MOVE V(1),Gx(1)
190  DRAW V(1),Gx(1)
200  FOR D=2 TO I
210     Gx(D)=G(D)*10^7
220     DRAW V(D),Gx(D)
230  NEXT D
240  FOR D=I+1 TO J
250     Gx(D)=G(D)*10^7
260     DRAW V(D),Gx(D)
270  NEXT D
280                                     !-----!
290  PRINT CHR$(12)
300  PRINT CHR$(129)
310  PRINT TABXY(10,10); " Would you like to have a paper of your G/V curve
? (y or n) "
320  INPUT P$
330  IF P$("<"Y" AND P$("<"y" AND P$("<"N" AND P$("<"n" THEN 320
340  IF P$="N" OR P$="n" THEN 480
350  PRINT TABXY(10,10); " If you would like to print the curve by printer,p
lease press key 'A' "
360  PRINT TABXY(10,11); " If you would like to plot the curve by plotter,pl
ease press any key. "
370  INPUT Pr$
380  IF Pr$="A" THEN
390     PRINT CHR$(131)
400     PRINT TABXY(25,16); " PRINTER IS READY,PRESS CONTINUE KEY "
410     PAUSE
420     PRINT CHR$(12)
430     DUMP GRAPHICS #701
440     ELSE
450     LOADSUB Plotter FROM "DHA10"
460     Plotter
470     PRINT CHR$(12)
480  END IF
490  GRAPHICS OFF
500  SUBEND

```

```

10                                     !!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20                                     !! DATA RECORDING PROGRAM !!
30                                     !!   "DHA14"   !!
40                                     !!!!!!!!!!!!!!!!!!!!!!!!!!!!!
50 SUB Record
60 ! I,J      are the counters of set of input data.
70 ! A,B,Amx,Amin,Bmx,Bmin are the dummy variables.
80 ! Vcmax,Vcmin are the values of voltage which capacitance is -
90 !           maximum and minimum, respectively.
100 ! Vgmax,Vgmin are the values of voltage which conductance is -
110 !           maximum and minimum, respectively.
120 ! Vdmax,Vdmin are the values of voltage which disipation factor-
130 !           is maximum and minimum, respectively.
140 ! F$      keeps the name of data file which is created.
150 ! L       is the variable to point each set of data kepted in files.
160 ! Msi     is the variable to keep the number of mass storage.
170
180 COM V(*),C(*),G(*),D(*)
190 COM REAL K1,K2,Y,C$,K$
200 COM REAL Amx,Amin,Bmx,Bmin,Vcmax,Vcmin,Vgmax,Vgmin,INTEGER I,J,Op
210
220 PRINT CHR$(12)
230 PRINT CHR$(129)
240 PRINT TABXY(1,10); " PLEASE INPUT THE NAME OF DATA FILE,SHOULD GIVE IN
FORM 'CG1,CD2,etc.' DEPEND "
250 PRINT TABXY(1,11); "                               ON TYPE OF DATA.

260 LINPUT F$
270 PRINT CHR$(12)
280 PRINT CHR$(129)
290 PRINT TABXY(10,10); " WOULD YOU LIKE TO RECORD YOUR DATA IN MSI #";CHR$(
(131); " 0";CHR$(129); " OR #";CHR$(131); " 1";CHR$(129); " ?"
300 INPUT Msi
310 IF Msi=0 OR Msi=1 THEN 370
320 PRINT CHR$(128)
330 PRINT TABXY(10,12); " PLEASE PRESS ONLY '1' OR '0' "
340 WAIT 3
350 PRINT TABXY(10,12); "
360 GOTO 300
370 IF Msi=0 THEN
380 MASS STORAGE IS ":,700,0"
390 ELSE
400 MASS STORAGE IS ":,700,1"
410 END IF
420 PRINT CHR$(131)
430 PRINT TABXY(10,17); " PLEASE WAIT A MOMENT,PROGRAM IS RECORDING YOUR DA
TA. "
440 CREATE BDAT F$,J+11,24
450 ASSIGN @File TO F$
460 OUTPUT @File,1;Amx
470 OUTPUT @File,2;Bmx
480 OUTPUT @File,3;Amin
490 OUTPUT @File,4;Bmin
500 OUTPUT @File,5;Vcmax
510 OUTPUT @File,6;Vgmax

```

```
520 OUTPUT @File,7;Vcmin
530 OUTPUT @File,8;Vgmin
540 OUTPUT @File,9;C$
550 OUTPUT @File,10;I
560 OUTPUT @File,11;J
570 FOR L=1 TO J
580     IF K$="A" THEN
590         OUTPUT @File,L+11;V(L),C(L),G(L)
600         ELSE
610         OUTPUT @File,L+11;V(L),C(L),D(L)
620     END IF
630 NEXT L
640 PRINT CHR$(128)
650 PRINT TABXY(10,17); "
.
660 MASS STORAGE IS ":,700,1"
670 BEEP
680 SUBEND
```



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10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20          !! RESISTANCE MEASUREMENT PROGRAM !!
30          !!           *RESIST*           !!
40          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
50          PRINT CHR$(12)
60          PRINT CHR$(128)
70          PRINT TABXY(15,1);"*****"
80          PRINT TABXY(15,2);"**           Resistance measurement program.           **"
90          PRINT TABXY(15,3);"*****"
100         PRINT TABXY(15,5);"This program is used for measuring the diffused resist
or by"
110        PRINT TABXY(10,6);"4140B pA meter/DC voltage source. The resistance of th
e resistor"
120        PRINT TABXY(10,7);"which you would like to measure should not be too smal
l,10 ohms."
130        PRINT TABXY(10,8);"Because you may get the error from the measurement."
140        PRINT TABXY(15,9);"Before you will measure the resistor by this program,p
lease"
150        PRINT TABXY(10,10);"warm up the 4140B for an hour and connect the I-INPUT
and Va-OUT"
160        PRINT TABXY(10,11);"PUT PROBE of the 4140B with the connector of the prob
e station."
170        PRINT CHR$(131)
180        PRINT TABXY(15,18);" WHEN YOU ARE READY,PLEASE PRESS THE 'CONTINUE' KEY.
"
190        PAUSE
200        !-----!
210        DIM I(500),R(500)
220        PRINT CHR$(12)
230        PRINT CHR$(129)
240        PRINT TABXY(15,10);" HOW MANY RESISTORS WOULD YOU LIKE TO MEASURE NOW ? "
250        INPUT X
260        IF X=0 THEN 520
270        V=.1
280        V$=VAL$(V)
290        REDIM I(X),R(X)
300        !-----!
310        OUTPUT 716;"R12"
320        WAIT 1
330        OUTPUT 716;"Z"
340        OUTPUT 716;"W7"
350        OUTPUT 716;"F1"
360        OUTPUT 716;"RA1"
370        OUTPUT 716;"H12"
380        OUTPUT 716;"J1"
390        OUTPUT 716;"W2"
400        OUTPUT 716;"A5"
410        OUTPUT 716;"B2"
420        OUTPUT 716;"L3"
430        OUTPUT 716;"PA";V$
440        !-----!
450        FOR J=1 TO X
460            PRINT CHR$(129)
470            PRINT TABXY(10,10);" PLEASE CONNECT YOUR RESISTOR WITH THE CONNECTOR O
F pA METER. "

```

```

480 PRINT CHR$(131)
490 PRINT TABXY(10,12);" WHEN YOU ARE READY,PLEASE PRESS THE 'CONTINUE' KE
Y. "
500 PAUSE
510 OUTPUT 716;"W1"
520 ENTER 716;A
530 I(J)=A
540 R(J)=V/I(J)
550 PRINT CHR$(128)
560 PRINT TABXY(30,15);"
570 PRINT TABXY(30,15);"R";J;" = ";R(J)
580 NEXT J
590 PRINT CHR$(129)
600 PRINT TABXY(5,18);" IF YOU WANT TO DO THE NEXT STATE,PLEASE PRESS THE 'CO
NTINUE' KEY. "
610 PAUSE
620 PRINT CHR$(12)
630 PRINT CHR$(129)
640 PRINT TABXY(2,10);" PLEASE INPUT THE NAME OF DATA FILE TO KEEP THE RESIST
ANCE VALUES,SHOULD GIVE "
650 PRINT TABXY(2,11);" IN FORM 'RE1,RE2,etc.'.

660 INPUT F$
670 PRINT CHR$(12)
680 PRINT CHR$(128)
690 PRINT TABXY(10,10);"Would you like to store your data in MSI # ";CHR$(130
);"0";CHR$(128);" or # ";CHR$(130);"1";CHR$(128);" ?"
700 INPUT P
710 IF P<>0 AND P<>1 THEN 700
720 IF P=0 THEN
730 MASS STORAGE IS ":,700,0"
740 ELSE
750 MASS STORAGE IS ":,700,1"
760 END IF
770 PRINT CHR$(131)
780 PRINT TABXY(10,15);" PLEASE WAIT A MOMENT,PROGRAM IS RECORDING YOUR DATA.
"
790 CREATE BDAT F$,Y+1,B
800 ASSIGN @File TO F$
810 OUTPUT @File,1;X
820 FOR K=1 TO X
830 OUTPUT @File,K+1;R(K)
840 NEXT K
850 MASS STORAGE IS ":,700,1"
860 PRINT CHR$(12)
870 PRINT CHR$(129)
880 PRINT TABXY(10,10);" Now,you have already had the resistance data in your
disk. "
890 BEEP
900 LOAD "MENU"
910 END

```

```

10      !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20      !! READING RESISTANCE DATA PROGRAM !!
30      !!       "RESIST_OUT"       !!
40      !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
50      DIM R(500)
60      PRINT CHR$(12)
70      PRINT CHR$(129)
80      PRINT TABXY(4,10);" Please input your resistance data file whitch you want to see the data. "
90      INPUT F$
100     PRINT CHR$(12)
110     PRINT CHR$(129)
120     PRINT TABXY(10,10);" WOULD YOU LIKE TO RECALL YOUR DATA IN MSI # ";CHR$(131);"0";CHR$(129);" OR # ";CHR$(131);"1";CHR$(129);" ?"
130     INPUT P
140     IF P<>0 AND P<>1 THEN 130
150     IF P=0 THEN
160         MASS STORAGE IS ":,700,0"
170     ELSE
180         MASS STORAGE IS ":,700,1"
190     END IF
200     ASSIGN @File TO F$
210     ENTER @File,1;X
220     FOR J=1 TO X
230         ENTER @File,J+1;R(J)
240     NEXT J
250     MASS STORAGE IS ":,700,1"
260     PRINT CHR$(12)
270     PRINT CHR$(128)
280     FOR K=1 TO X/2
290         PRINTER IS 701
300         PRINT "R";K;" = ";R(K),"R";K+X/2;" = ";R(K+X/2)
310     NEXT K
320     PRINTER IS 1
330     LOAD "MENU"
340     END

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10          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
20          !! FINDING THRESHOLD VOLTAGE PROGRAM !!
30          !!           "MOS_T1"           !!
40          !!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
50      ! V1,V1$ is the variable keeping the starting voltage.
60      ! V2,V2$ is the variable keeping the stopping voltage.
70      ! Dv,Dv$ is the variable keeping the stepping voltage.
80      ! V10 is the variable keeping the voltage value at the drain current
90      !     10 uA.
100     ! V40 is the variable keeping the voltage value at the drain current
110     !     40 uA.
120     ! Vt is the threshold voltage.
130     PRINT CHR$(12)
140     PRINT CHR$(128)
150     PRINT TABXY(10,10);" Please input the voltage range which you want to
find the threshold"
160     PRINT TABXY(10,11);" voltage of MOSFET. "
170     PRINT CHR$(129)
180     PRINT TABXY(10,13);" WHAT IS THE STARTING VOLTAGE ? "
190     INPUT V1
200     IF V1<-100 OR V1>100 THEN
210         PRINT CHR$(131)
220         PRINT TABXY(10,15);" YOUR STARTING VOLTAGE IS OVER RANGE,PLEASE GIV
E THE NEW VALUE. "
230         GOTO 190
240     END IF
250     PRINT CHR$(128)
260     PRINT TABXY(10,15);"
"
270     PRINT CHR$(129)
280     PRINT TABXY(10,13);" WHAT IS THE STOPPING VOLTAGE ? "
290     INPUT V2
300     IF V2<-100 OR V2>100 THEN
310         PRINT CHR$(131)
320         PRINT TABXY(10,15);" YOUR STOPPING VOLTAGE IS OVER RANGE,PLEASE GIV
E THE NEW VALUE. "
330         GOTO 290
340     END IF
350     PRINT CHR$(128)
360     PRINT TABXY(10,15);"
"
370     PRINT CHR$(129)
380     PRINT TABXY(10,13);" WHAT IS THE STEP VOLTAGE OF STAIRCASE ? "
390     INPUT Dv
400     IF Dv<-10 OR Dv>10 THEN
410         PRINT CHR$(131)
420         PRINT TABXY(10,15);" YOUR STEP VOLTAGE IS OVER RANGE,PLEASE GIVE TH
E NEW VALUE. "
430         GOTO 390
440     END IF
450     PRINT CHR$(129)
460     PRINT TABXY(10,13);" WHAT IS THE CONSTANT VOLTAGE FOR THE DRAIN TERMIN
AL ? "
470     INPUT Vb
480     IF Vb<-100 OR Vb>100 THEN

```



```

490     PRINT CHR$(131)
500     PRINT TABXY(10,15);" YOUR DRAIN VOLTAGE IS OVER RANGE,PLEASE GIVE T
HE NEW VALUE. "
510     GOTO 470
520     END IF
530     PRINT CHR$(128)
540     PRINT TABXY(10,15);"
*
550     PRINT TABXY(10,13);"

560     PRINT CHR$(12)
570     PRINT CHR$(128)
580     PRINT TABXY(10,10);" The voltage range whitch you want to find the thr
eshold voltage"
590     PRINT TABXY(10,11);" is"
600     PRINT TABXY(25,13);" THE STARTING VOLTAGE IS ";V1;" V."
610     PRINT TABXY(25,14);" THE STOPPING VOLTAGE IS ";V2;" V."
620     PRINT TABXY(25,15);" THE STEP VOLTAGE IS ";Dv;" V."
630     PRINT TABXY(25,16);" THE DRAIN VOLTAGE IS ";Vb;" V."
640     Y=(V2-V1)/Dv
650     V1$=VAL$(V1)
660     V2$=VAL$(V2)
670     Dv$=VAL$(Dv)
680     Vb$=VAL$(Vb)
690     PRINT CHR$(129)
700     PRINT TABXY(15,18);" When you are ready,please press the 'CONTINUE' ke
y. "
710     PAUSE
720     !-----!
730     OUTPUT 716;"R12"
740     OUTPUT 716;"I"
750     OUTPUT 716;"W7"
760     OUTPUT 716;"F1"
770     OUTPUT 716;"RA1"
780     OUTPUT 716;"H12"
790     OUTPUT 716;"I2"
800     OUTPUT 716;"J1"
810     OUTPUT 716;"A3"
820     OUTPUT 716;"B1"
830     OUTPUT 716;"L3"
840     OUTPUT 716;"M3"
850     OUTPUT 716;"PB";Vb$
860     OUTPUT 716;"PS";V1$
870     OUTPUT 716;"PT";V2$
880     OUTPUT 716;"PE";Dv$
890     OUTPUT 716;"PH0.5"
900     OUTPUT 716;"W2"
910     OUTPUT 716;"W1"
920     !-----!
930     PRINT CHR$(12)
940     PRINT CHR$(128)
950     PRINT TABXY(15,5);"Please connect your sample following this connectio
n."
960     PRINT TABXY(10,7);"1. Gate is connected to VA terminal of pA meter."
970     PRINT TABXY(10,8);"2. Drain is connected to VB terminal of pA meter."

```

```

980 PRINT TABXY(10,9);"3. Source and the substrate are connected to the HI
GH terminal of pA -"
990 PRINT TABXY(10,10);" meter."
1000 PRINT TABXY(10,11);"4. The LOW terminal of pA meter is connected to th
e BROUD of system."
1010 PRINT CHR$(129)
1020 PRINT TABXY(10,18);" WHEN YOU ARE READY,PLEASE PRESS THE 'CONTINUE' KE
Y "
1030 PAUSE
1040 !-----!
1050 PRINT CHR$(12)
1060 PRINT CHR$(131)
1070 PRINT TABXY(15,10);" Please wait a moment,program is running. "
1080 FOR X=1 TO Y
1090 ENTER 716;A
1100 IF ABS((1.0E-4)-A)<=5.0E-6 THEN
1110 V100=V1+(Dv*X)
1120 END IF
1130 IF ABS((4.0E-4)-A)<=5.0E-6 THEN
1140 V400=V1+(Dv*X)
1150 END IF
1160 OUTPUT 716;"M6"
1170 NEXT X
1180 Vt=2*V100-V400
1190 PRINT CHR$(128)
1200 PRINT TABXY(10,10);"
1210 !-----!
1220 PRINT CHR$(12)
1230 PRINT CHR$(129)
1240 PRINT TABXY(15,10);" THRESHOLD VOLTAGE OF MOSFET IS ";Vt;" V "
1250 PRINT CHR$(128)
1260 PRINT TABXY(15,12);" V100 = ";V100;" V.,V400 = ";V400;" V.,Vd = ";Vb;"
V."
1270 BEEP
1280 PRINT CHR$(129)
1290 PRINT TABXY(10,18);" When you are ready,please press the CONTINUE key.
"
1300 PAUSE
1310 OUTPUT 716;"M7"
1320 LOAD "MENU"
1330 END

```

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ภาคผนวก ข.

เงื่อนไขของขั้นตอนการผลิตสิ่งประดิษฐ์มอส

การทำ Final cleaning

1. ล้างแวนผลึกใน Trichloroethylene ด้วย Ultrasonic cleaner (ร้อน) นาน 10 นาที
2. ล้างแวนผลึกใน Acetone ด้วย Ultrasonic cleaner (ร้อน) นาน 10 นาที
3. ล้างแวนผลึกใน DI water ด้วย Ultrasonic cleaner (ร้อน) นาน 10 นาที
4. เปลี่ยน DI water ใหม่และล้างแวนผลึกใน DI water ด้วย Ultrasonic cleaner (ร้อน) อีก 10 นาที
5. เป่าแห้งด้วยก๊าซ N_2
6. นำแวนผลึกจุ่มลงใน HNO_3 (70%) เตือนาน 10 นาที
7. ล้างแวนผลึกด้วย DI water และเป่าแห้งด้วยก๊าซ N_2
8. นำแวนผลึกจุ่มลงใน Buffer HF 1 นาที
9. ล้างแวนผลึกด้วย DI water และเป่าแห้งด้วยก๊าซ N_2

การทำ Photolithography โดยใช้ Positive photoresist

เป็นกระบวนการถ่ายแบบจากหน้ากากที่ได้ออกแบบไว้ (ฟิล์มกระจก) ลงบนแวนผลึก โดยใช้ photoresist ชนิด positive ของ Shipley รุ่น AZ1350

จุฬาลงกรณ์มหาวิทยาลัย

ขั้นตอนในการทำ Photolithography มีดังนี้คือ

1. อบแวนผลึกในเตาอุณหภูมิ $120^\circ C$ นาน 30 นาที
2. เคลือบ Photoresist ลงบนแวนผลึกด้วย Spinner ที่ความเร็ว 5000 รอบ/นาที นาน 20 วินาที
3. อบแห้งแวนผลึกในเตาอุณหภูมิ $80^\circ C$ เป็นเวลา 30 นาที

4. นำแว่นผลึกมาถ่ายแบบโดยฉายแสงอุลตราไวโอเลตนาน 20 วินาที
5. Develop ด้วยน้ำยาเคมีนาน 1 นาที
6. ล้างแว่นผลึกด้วย DI water และเป่าแห้งด้วยก๊าซ N_2
7. อบแห้งแว่นผลึกในเตาอุณหภูมิ $120^{\circ}C$ นาน 15 นาที

การทำ Photolithography โดยใช้ Negative photoresist

เป็นกระบวนการถ่ายแบบจากหน้ากากที่ได้ออกแบบไว้ โดยใช้ Photoresist ชนิด negative รุ่น OMR-83

ขั้นตอนในการทำ Photolithography มีดังนี้คือ

1. ล้างแว่นผลึกด้วย Trichloroethylene, Acetone และน้ำ DI
2. เป่าแห้งด้วยก๊าซ N_2
3. อบแว่นผลึกในเตาอุณหภูมิ $120^{\circ}C$ นาน 30 นาที
4. เคลือบ Photoresist ลงบนแว่นผลึกด้วย Spinner ที่ความเร็ว 4000 รอบ/นาที นาน 20 วินาที
5. อบแห้งแว่นผลึกในเตาอุณหภูมิ $70^{\circ}C$ นาน 20 นาที
6. นำแว่นผลึกมาถ่ายแบบโดยฉายแสงอุลตราไวโอเลตนาน 20 วินาที
7. Develop ด้วยน้ำยา OMR-SL เป็นเวลา 3 นาที
8. ล้างน้ำยา Developer OMR-SL ออกจากแว่นผลึกด้วยน้ำยา OMR-Butyl acetate
9. เป่าแห้งด้วยก๊าซ N_2
10. อบแห้งแว่นผลึกในเตาอุณหภูมิ $120^{\circ}C$ นาน 25 นาที

การล้าง Photoresist OMR-83 ออกจากแว่นผลึกหลังจากการกัดลุมิเนียมเรียบร้อยแล้ว ทำโดยการจุ่มแว่นผลึกลงใน Stripper OMR-502 เตือนาน 2 นาที

ภาคผนวก ก.

การคำนวณลักษณะสมบัติของสิ่งประดิษฐ์ MOS ทางทฤษฎี

MOS Capacitor Characteristics (4)

$$q : = 1.602 \times 10^{-19} \quad [\text{Electron Charge (Coulomb)}]$$

$$Q_{ss} : = 6.2 \times 10^{11} * q \quad [\text{Interface state density (Coulomb/cm(2))}]$$

$$N_a : = 1.0 \times 10^{15} \quad [\text{Substrate concentration (cm}^{-3}\text{)}]$$

$$n_i : = 1.5 \times 10^{10} \quad [\text{Intrinsic concentration (cm}^{-3}\text{)}]$$

$$k : = 1.38 \times 10^{-23} \quad [\text{Boltzmann constant (J/K)}]$$

$$\epsilon_s : = 1.04 \times 10^{-12} \quad [\text{Si permittivity (F/cm)}]$$

$$\epsilon_{ox} : = 3.45 \times 10^{-13} \quad [\text{SiO}_2 \text{ permittivity (F/cm)}]$$

$$A : = .0025 \quad [\text{Gate area (cm}^2\text{)}]$$

$$d : = 1.0 \times 10^{-5} \quad [\text{Gate oxide thickness (cm)}]$$

$$C_{ox} : = \frac{\epsilon_{ox} * A}{d} * 10^{12} \quad [\text{Oxide capacitance (pF)}]$$

$$C_{ox} = 86.25$$

$$C_{oxa} : = \frac{C_{ox}}{A} * 10^{-12} \quad [\text{Oxide capacitance per unit area (F/cm}^2\text{)}]$$

$$C_{oxa} = 3.45 \times 10^{-8}$$

$$V_{ox} : = \frac{Q_{ss}}{C_{oxa}} \quad V_{ox} = 2.879 \quad (\text{Volts})$$

$$T : = 300 \quad (\text{Kelvin})$$

$$V_q : = -20.5 \quad (\text{Volts})$$

$$X : = 0 \dots 50$$

$$V_{1X} : = V_q + X \quad [\text{Surface potential (Volts)}]$$

$$V_X : = V_{1X} + V_{ox} \quad [\text{Gate voltage (volts)}]$$

$$U_b : = \ln \left[\frac{N_a}{n_i} \right] \quad (\text{Volts})$$

$$C_{fbs} : = A \sqrt{\frac{\epsilon_s \cdot q^2 \cdot N_a}{k \cdot T}} \cdot 10^{12} \quad [\text{Surface flatband capacitance (pF)}]$$

$$C_{fbs} = 200.733$$

$$C_{fb} : = \frac{C_{fbs} \cdot C_{ox}}{C_{fbs} + C_{ox}} \quad [\text{Flatband capacitance (pF)}]$$

$$C_{fb} = 60.328$$

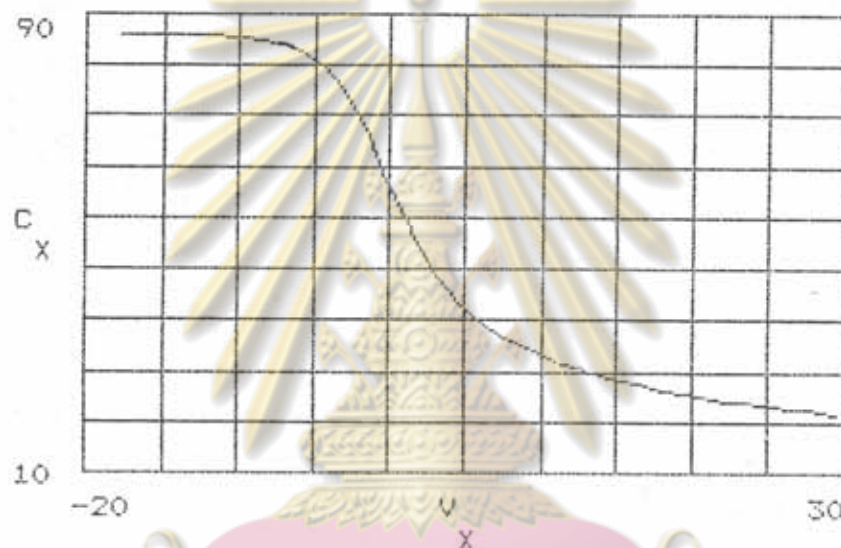
$$F_X : = 2 \cdot V_X + \exp[-V_X] - 1$$

$$\Delta_{\alpha X} : = \left[\frac{F_X}{\exp[V_X] - 1} \right] \int_0^{V_X} \left[\frac{\exp(V_s) - \exp(-V_s) - 2 \cdot V_s}{[2 \cdot V_s + \exp(-V_s) - 1 + \exp(2 \cdot U_b) \cdot (\exp[V_X] - 1)]^3} \right] dV_s - 1$$

$$Y_X : = \text{if } [V_X > 0, 1, -1] \text{ [Sqn. Fn]}$$

$$C_{S_X} : = Y_X * C_{fbs} * \frac{1 - \exp[-V_X] + \left[\frac{n_i}{N_a}\right]^2 * [\exp[V_X] - 1] * \left[\frac{\text{Delta}_X}{1 + \text{Delta}_X}\right] + 1}{F_X}$$

$$C_X : = \frac{C_{S_X} * C_{ox}}{C_{S_X} + C_{ox}} \quad \text{[MOS capacitance (pF)]}$$



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CHARACTERISTICS of MOSFET : W=700. um,L=50 um (38)

$q := 1.6 \cdot 10^{-19}$ [Electron charge (Coulomb)]
 $\mu := 1360$ [Electron mobility (cm²/volt*sec)]
 $\epsilon_s := 1.04 \cdot 10^{-12}$ [Si permittivity]
 $E_{afs} := 4.23$ [Electron affinity (Volts)]
 $W_{fm} := 4.2$ [Work function of Al (Volts)]
 $E_g := 1.12$ [Band gap energy of Si]
 $K_b := 1.38 \cdot 10^{-23}$ [Boltzman constant (J/K)]
 $T := 300$ [Room temperature (Kelvin)]
 $N_a := 1.0 \cdot 10^{15}$ [Substrate concentration (cm⁻³)]
 $n_i := 1.5 \cdot 10^{10}$ [Intrinsic concentration (cm⁻³)]
 $W_{ms} := W_{fm} - \left[E_{afs} - \frac{E_g}{2} - K_b \cdot T \cdot \ln \left[\frac{n_i}{N_a} \right] \right]$ $W_{ms} = 0.53$
 [W_{ms} - Work function difference (Volts)]
 $\phi_b := \frac{K_b \cdot T \cdot \ln \left[\frac{N_a}{n_i} \right]}{q}$ $\phi_b = 0.287$ [Volts]
 $Q_{ss} := 6.3 \cdot 10^{11}$ [Interface state density (cm⁻²)]
 $A := .0025$ [Gate area (cm²)]
 $C_{ox} := 86.25 \cdot 10^{-12}$ [Oxide capacitance (Farad)]
 $C_{oxa} := \frac{C_{ox}}{A}$ [Farad/cm²]
 [C_{oxa} - Oxide capacitance per unit area]

$$V_{fb} := W_{ms} - \frac{Q_{ss} \cdot Q}{C_{oxa}} \quad V_{fb} = -2.392 \quad [\text{Volts}]$$

[Vfb - Flat-band voltage]

$$\Gamma := \frac{\sqrt{2 \cdot \epsilon_s \cdot q \cdot N_a}}{C_{ox}} \cdot A \quad \Gamma = 0.529$$

[Γ - Body-effect parameter]

$$V_{th} := V_{fb} + 2 \cdot \phi_b + \Gamma \cdot \sqrt{2 \cdot \phi_b} \quad V_{th} = -1.416 \quad [\text{Volts}]$$

[Vth - Threshold voltage]

$$W_g := 700 \quad [\text{Width of gate } (\mu\text{m})]$$

$$L_{eff} := 50 \quad [\text{Length of gate } (\mu\text{m})]$$

$$\beta := \frac{\mu \cdot C_{oxa} \cdot W_g}{L_{eff}} \quad \beta = 6.569 \cdot 10^{-4}$$

$$I_{dss} := \frac{\beta}{2} \cdot (0 - V_{th})^2 \quad I_{dss} = 6.586 \cdot 10^{-4}$$

[Idss - Drain current at zero gate bias (Amp)]

$$V_{qa} := -0.182 \quad [V_{qa} - \text{Gate voltage at } I_{ds}=500 \mu\text{A (Volts)}]$$

$$G_m := \beta \cdot (V_{qa} - V_{th}) \quad G_m = 8.106 \cdot 10^{-4}$$

[Gm - Transconductance (mhos)]

$$V_{qs} := 1.0 \quad [\text{Starting gate voltage (Volts)}]$$

$$X := 0 \dots 10$$

$$V_g := V_{qs} + (X \cdot 1.0) \quad [\text{Gate voltage (Volts)}]$$

$$V_{ds} := 0 \quad [\text{Starting drain-source voltage (Volts)}]$$

$$Y := 0 \dots 100$$

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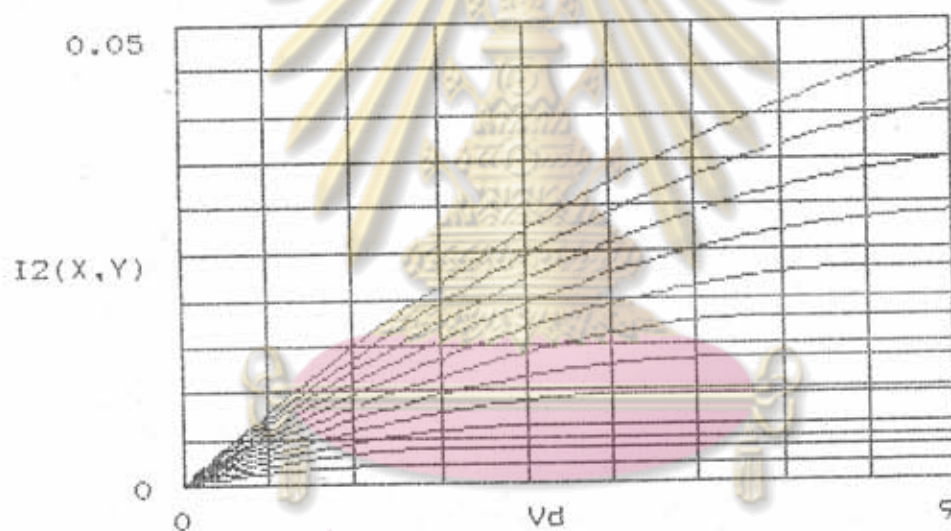
$$V_{dY} := V_{ds} + (Y \cdot 0.1) \quad [\text{Drain-source voltage (Volts)}]$$

$$I(X, Y) := \beta \cdot \left[\left[\frac{V_{qX} - V_{th}}{X} \right] \cdot \frac{V_{dY}}{Y} - \frac{V_{dY}^2}{2Y} \right]$$

$$I1(X, Y) := \frac{\beta}{2} \cdot \left[\frac{V_{qX} - V_{th}}{X} \right]^2$$

$$V_{dssatX} := \frac{V_{qX} - V_{th}}{X}$$

$$I2(X, Y) := \text{if} \left[\frac{V_{dY}}{Y} \geq V_{dssatX}, I1(X, Y), I(X, Y) \right]$$



$I(X, Y)$ - Drain current (linear region)

$I1(X, Y)$ - Drain current (saturation region)

$I2(X, Y)$ - Drain current

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CHARACTERISTICS of MOSFET : W=700 um,L=75 um (33)

$q := 1.6 \cdot 10^{-19}$ [Electron charge (Coulomb)]
 $\mu := 1360$ [Electron mobility (cm²/volt*sec)]
 $\epsilon_s := 1.04 \cdot 10^{-12}$ [Si permittivity]
 $E_{afs} := 4.23$ [Electron affinity (Volts)]
 $W_{fm} := 4.2$ [Work function of Al (Volts)]
 $E_g := 1.12$ [Band gap energy of Si]
 $k_b := 1.38 \cdot 10^{-23}$ [Boltzman constant (J/K)]
 $T := 300$ [Room temperature (Kelvin)]
 $N_a := 1.0 \cdot 10^{15}$ [Substrate concentration (cm⁻³)]
 $n_i := 1.5 \cdot 10^{10}$ [Intrinsic concentration (cm⁻³)]
 $W_{ms} := W_{fm} - \left[E_{afs} - \frac{E_g}{2} - k_b \cdot T \cdot \ln \left[\frac{n_i}{N_a} \right] \right]$ $W_{ms} = 0.53$
 [W_{ms} - Work function difference (Volts)]
 $\phi_b := \frac{k_b \cdot T \cdot \ln \left[\frac{N_a}{n_i} \right]}{q}$ $\phi_b = 0.287$ [Volts]
 $q_{ss} := 6.3 \cdot 10^{11}$ [Interface state density (cm⁻²)]
 $A := .0025$ [Gate area (cm²)]
 $C_{ox} := 86.25 \cdot 10^{-12}$ [Oxide capacitance (Farad)]
 $C_{oxa} := \frac{C_{ox}}{A}$ [Farad/cm²]
 [C_{oxa} - Oxide capacitance per unit area]

$$V_{fb} := W_{ms} - \frac{Q_{ss} \cdot Q}{C_{oxa}} \quad V_{fb} = -2.392 \quad [\text{Volts}]$$

[V_{fb} - Flat-band voltage]

$$\Gamma := \frac{\sqrt{2 \cdot \epsilon_s \cdot Q \cdot N_a}}{C_{ox}} \cdot A \quad \Gamma = 0.529$$

[Γ - Body-effect parameter]

$$V_{th} := V_{fb} + 2 \cdot \phi_b + \Gamma \cdot \sqrt{2 \cdot \phi_b} \quad V_{th} = -1.416 \quad [\text{Volts}]$$

[V_{th} - Threshold voltage]

$$W_g := 700 \quad [\text{Width of gate } (\mu\text{m})]$$

$$L_{eff} := 75 \quad [\text{Length of gate } (\mu\text{m})]$$

$$\beta := \frac{\mu \cdot C_{oxa} \cdot W_g}{L_{eff}} \quad \beta = 4.379 \cdot 10^{-4}$$

$$I_{dss} := \frac{\beta}{2} \cdot (0 - V_{th})^2 \quad I_{dss} = 4.39 \cdot 10^{-4}$$

[I_{dss} - Drain current at zero gate bias (Amp)]

$$V_{qa} := 0.095 \quad [V_{qa} - \text{Gate voltage at } I_{ds}=500 \mu\text{A (Volts)}]$$

$$G_m := \beta \cdot (V_{qa} - V_{th}) \quad G_m = 6.617 \cdot 10^{-4}$$

[G_m - Transconductance (mhos)]

$$V_{qs} := 1.0 \quad [\text{Starting gate voltage (Volts)}]$$

$$X := 0 \dots 10$$

$$V_g := V_{qs} + (X \cdot 1.0) \quad [\text{Gate voltage (Volts)}]$$

$$V_{ds} := 0 \quad [\text{Starting drain-source voltage (Volts)}]$$

$$Y := 0 \dots 100$$

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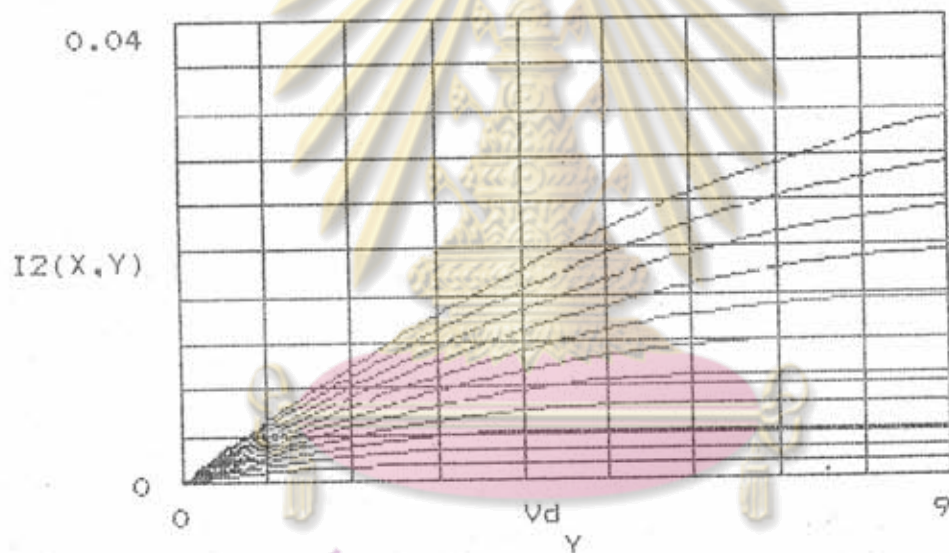
$$V_{dY} := V_{ds} + (Y \cdot 0.1) \quad [\text{Drain-source voltage (Volts)}]$$

$$I(X, Y) := \beta \cdot \left[\left[\frac{V_{qX} - V_{th}}{X} \right] \cdot V_{dY} - \frac{V_{dY}^2}{2} \right]$$

$$I1(X, Y) := \frac{\beta}{2} \cdot \left[\frac{V_{qX} - V_{th}}{X} \right]^2$$

$$V_{dssatX} := \frac{V_{qX} - V_{th}}{X}$$

$$I2(X, Y) := \text{if} \left[\frac{V_{dY}}{Y} \geq V_{dssatX}, I1(X, Y), I(X, Y) \right]$$



$I(X, Y)$ - Drain current (linear region)

$I1(X, Y)$ - Drain current (saturation region)

$I2(X, Y)$ - Drain current

จุฬาลงกรณ์มหาวิทยาลัย

CHARACTERISTICS of MOSFET : W=700 um,L=100 um (33)

$q := 1.6 \cdot 10^{-19}$ [Electron charge (Coulomb)]
 $\mu := 1360$ [Electron mobility (cm²/volt*sec)]
 $\epsilon_s := 1.04 \cdot 10^{-12}$ [Si permittivity]
 $E_{afs} := 4.23$ [Electron affinity (Volts)]
 $W_{fm} := 4.2$ [Work function of Al (Volts)]
 $E_g := 1.12$ [Band gap energy of Si]
 $K_b := 1.38 \cdot 10^{-23}$ [Boltzman constant (J/K)]
 $T := 300$ [Room temperature (Kelvin)]
 $N_a := 1.0 \cdot 10^{15}$ [Substrate concentration (cm⁻³)]
 $n_i := 1.5 \cdot 10^{10}$ [Intrinsic concentration (cm⁻³)]
 $W_{ms} := W_{fm} - \left[E_{afs} - \frac{E_g}{2} - K_b \cdot T \cdot \ln \left[\frac{n_i}{N_a} \right] \right]$ $W_{ms} = 0.53$
 [W_{ms} - Work function difference (Volts)]
 $\phi_b := \frac{K_b \cdot T \cdot \ln \left[\frac{N_a}{n_i} \right]}{q}$ $\phi_b = 0.287$ [Volts]
 $Q_{ss} := 6.3 \cdot 10^{11}$ [Interface state density (cm⁻²)]
 $A := 1.0025$ [Gate area (cm²)]
 $C_{ox} := 86.25 \cdot 10^{-12}$ [Oxide capacitance (Farad)]
 $C_{oxa} := \frac{C_{ox}}{A}$ [Farad/cm²]
 [C_{oxa} - Oxide capacitance per unit area]

$$V_{fb} := W_{ms} - \frac{Q_{ss} \cdot Q}{C_{oxa}} \quad V_{fb} = -2.392 \quad [\text{Volts}]$$

[Vfb - Flat-band voltage]

$$\Gamma := \frac{\sqrt{2 \cdot \epsilon_s \cdot Q \cdot N_a}}{C_{ox}} \cdot A \quad \Gamma = 0.529$$

[Γ - Body-effect parameter]

$$V_{th} := V_{fb} + 2 \cdot \phi_b + \Gamma \cdot \sqrt{2 \cdot \phi_b} \quad V_{th} = -1.416 \quad [\text{Volts}]$$

[Vth - Threshold voltage]

$$W_q := 700 \quad [\text{Width of gate } (\mu\text{m})]$$

$$L_{eff} := 100 \quad [\text{Length of gate } (\mu\text{m})]$$

$$\beta := \frac{\mu \cdot C_{oxa} \cdot W_q}{L_{eff}} \quad \beta = 3.284 \cdot 10^{-4}$$

$$I_{dss} := \frac{\beta}{2} \cdot (0 - V_{th})^2 \quad I_{dss} = 3.293 \cdot 10^{-4}$$

[Idss - Drain current at zero gate bias (Amp)]

$$V_{qa} := 0.33 \quad [V_{qa} - \text{Gate voltage at } I_{ds}=500 \mu\text{A (Volts)}]$$

$$G_m := \beta \cdot (V_{qa} - V_{th}) \quad G_m = 5.735 \cdot 10^{-4}$$

[Gm - Transconductance (mhos)]

$$V_{qs} := 1.0 \quad [\text{Starting gate voltage (Volts)}]$$

$$X := 0 \dots 10$$

$$V_q := V_{qs} + (X \cdot 1.0) \quad [\text{Gate voltage (Volts)}]$$

$$V_{ds} := 0 \quad [\text{Starting drain-source voltage (Volts)}]$$

$$Y := 0 \dots 100$$

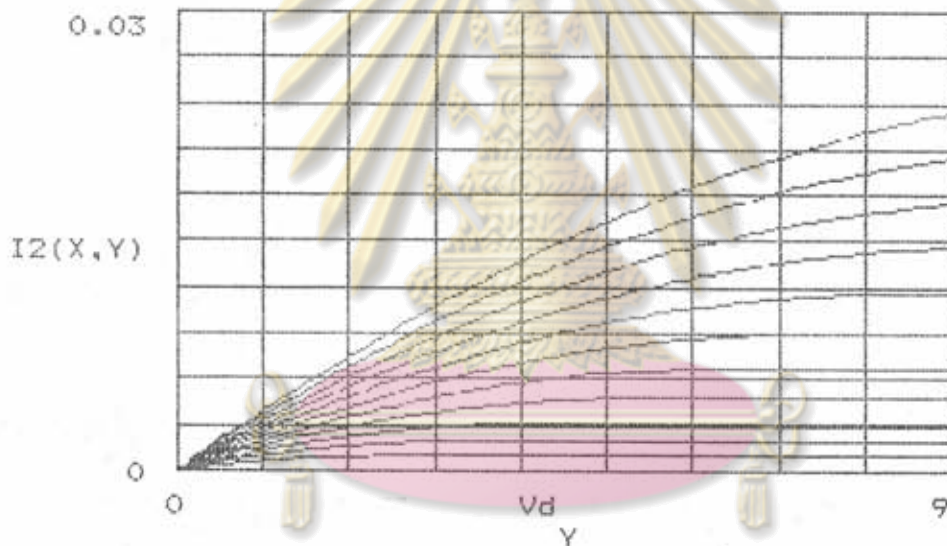
$$V_{dY} := V_{ds} + (Y \cdot 0.1) \quad [\text{Drain-source voltage (Volts)}]$$

$$I(X, Y) := \beta \cdot \left[\left[\frac{V_{qX}}{X} - V_{th} \right] \cdot V_{dY} - \frac{V_{dY}^2}{2} \right]$$

$$I1(X, Y) := \frac{\beta}{2} \left[\frac{V_{qX}}{X} - V_{th} \right]^2$$

$$V_{dssatX} := \frac{V_{qX}}{X} - V_{th}$$

$$I2(X, Y) := \text{if} \left[\frac{V_{dY}}{Y} \geq V_{dssatX}, I1(X, Y), I(X, Y) \right]$$



$I(X, Y)$ - Drain current (linear region)

$I1(X, Y)$ - Drain current (saturation region)

$I2(X, Y)$ - Drain current

$$G_{m50} := 8.106 \cdot 10^{-4} \quad [\text{mho}] \quad G_{m75} := 6.617 \cdot 10^{-4} \quad [\text{mho}]$$

$$G_{m100} := 5.735 \cdot 10^{-4} \quad [\text{mho}]$$

$$A := \frac{G_{m50}}{G_{m100}} \quad A = 1.413$$

$$B := \frac{G_{m75}}{G_{m100}} \quad B = 1.154$$



ประวัติผู้เขียน

นายธนวิษฐ์ ชุติกาวิทย์ เกิดเมื่อวันที่ 3 กุมภาพันธ์ 2505 ณ จังหวัดสระบุรี สำเร็จการศึกษาปริญญาวิศวกรรมศาสตรบัณฑิต สาขาวิศวกรรมไฟฟ้า จากคณะวิศวกรรมศาสตร์ มหาวิทยาลัยเชียงใหม่ เมื่อปี พ.ศ. 2528 หลังจากนั้นได้เข้ารับราชการที่คณะวิศวกรรมศาสตร์ มหาวิทยาลัยเชียงใหม่ เป็นเวลา 1 ปี จึงลาศึกษาต่อในระดับปริญญาโทบัณฑิต ๓ คณะ-วิศวกรรมศาสตร์ จุฬาลงกรณ์มหาวิทยาลัย



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